

Emerging semiconductors meet new applications: security, multi-valued computing, and hazard monitoring

- Material-Device-Circuit Co-Consideration

Hocheon Yoo

**Associate Professor of Electronic Engineering
Head Professor of Graduate School
(Nano Science and Technology Convergence)**

Gachon University

Introduction



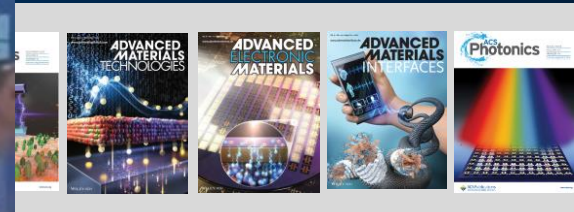
Postdoc, Northwestern Univ. (2019)
 Ph.D., POSTECH (2018)
 Visiting scholar, Holst Centre, Netherl
 B.S., Hanyang Univ. (2014)



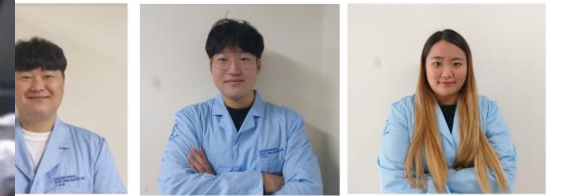
Done Hyun Lee, PhD student
 Jaehyun Park, PhD student
 Seonjae Kim, MS student



Yunhae Jeon, BS/MS student
 Jihyun Shin, BS/MS student
 Minseo Kim, BS student



(2022,2023)
 Excellence, (2022, 2023)
 (2021)
 Award, (2021, 2023)



Yungho Choi, PhD student
 Younmin Han, MS student
 Seunghye Kang, MS student



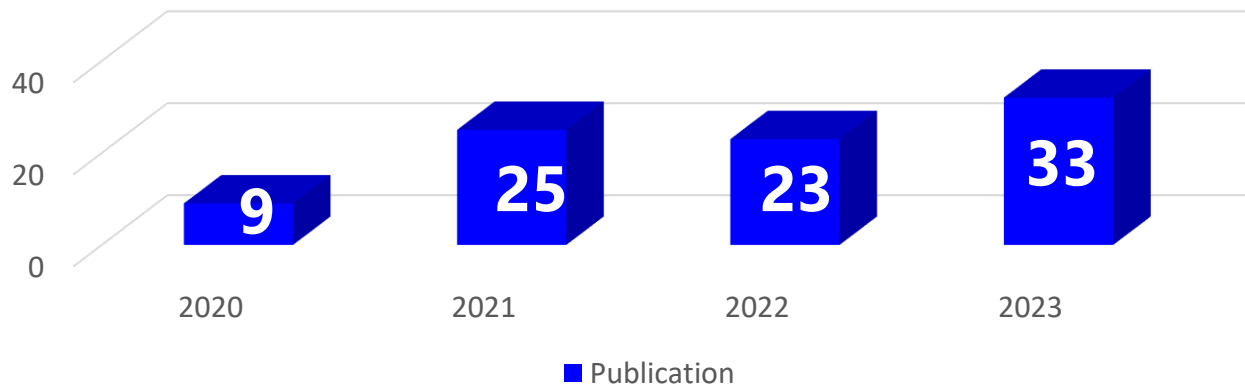
Yungho Jo, BS/MS student
 Jisoo Park, MS/BS student
 Yeo Eun Kim, MS student

Gachon Academic Top 1 (2022,203)
 Gachon one of largest Lab (2022)

The SDC Research Lab develops
 a material-device-process co-innovation approach.



Publication



Energy Band Engineering by Remote Doping of Self-Assembled Monolayer Leads to High-Performance IGZO/p-Si Heterostructure Photodetectors. **Advanced Materials**, IF: 32.09

Vertically-Integrated Electronics: New Opportunities from Emerging Materials and Devices. **Nano-Micro Letters**, IF: 23.655

A reconfigurable binary/ternary logic conversion-in-memory based on drain-aligned floating-gate heterojunction transistors. **Nature Communications**, IF: 17.69

Machine Learning Attacks-Resistant Security by Mixed-Assembled Layers-Inserted Graphene Physically Unclonable Function. **Advanced Science**, IF: 17.521

Vertically-Stacked, Low-Voltage Organic Ternary Logic Circuits Including Nonvolatile Floating-Gate Memory Transistors. **Nature Communications**, IF: 17.69

Strengthening Multi-Factor Authentication through Physically Unclonable Functions. **Advanced Science**, IF: 17.52

Charge Transport Advancement in Anti-Ambipolar Transistors: Spatially Separating Layer Sandwiched between N-type Metal Oxides and P-type Small Molecules. **Advanced Functional Materials**, IF: 19.924

Nanoscale Channel Gate-Tunable Diodes Obtained by Asymmetric Contact and Adhesion Lithography on Fluoropolymers. **Small**, IF: 15.153

Contributions of Light to Novel Logic Concepts using Optoelectronic Materials **Small Methods**, IF: 15.367

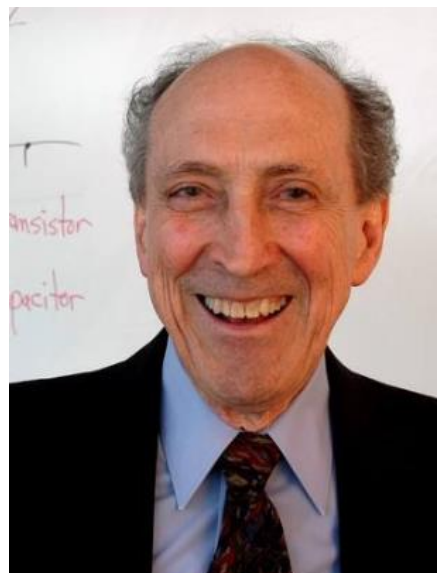
Boosting the Optoelectronic Properties of Molybdenum Diselenide by Combining Phase Transition Engineering with Organic Cationic Dye Doping. **ACS nano**, IF: 15.881

Unpredictably Disordered Distribution of Hetero-blended Graphene Oxide Flakes with Non-identical Resistance in Physical Unclonable Functions. **Advanced Functional Materials**, IF: 19.924

Background

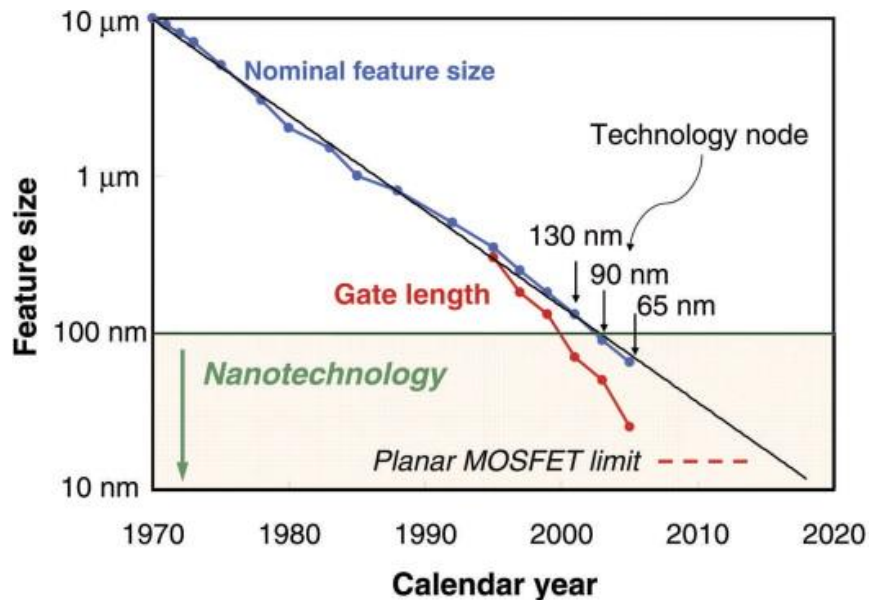


Gordon Moore



Robert Dennard

Thompson, Scott E., and Srivatsan Parthasarathy. Materials today 9.6 (2006): 20-25.



😊 Lower power consumption

😊 Higher operating frequency

☹ Scaling limit →

New Materials

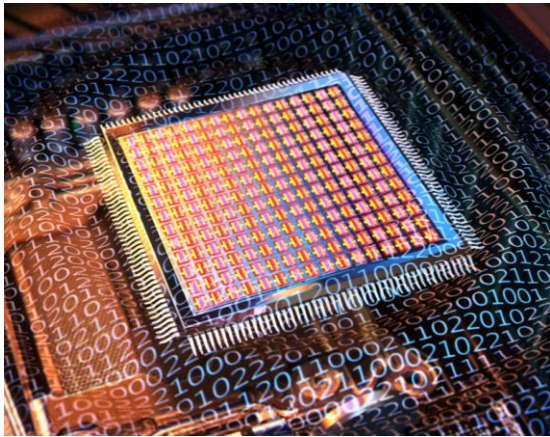
New Devices

New Circuits

WHAT'S
NEXT



Multi-valued logic



Security Devices

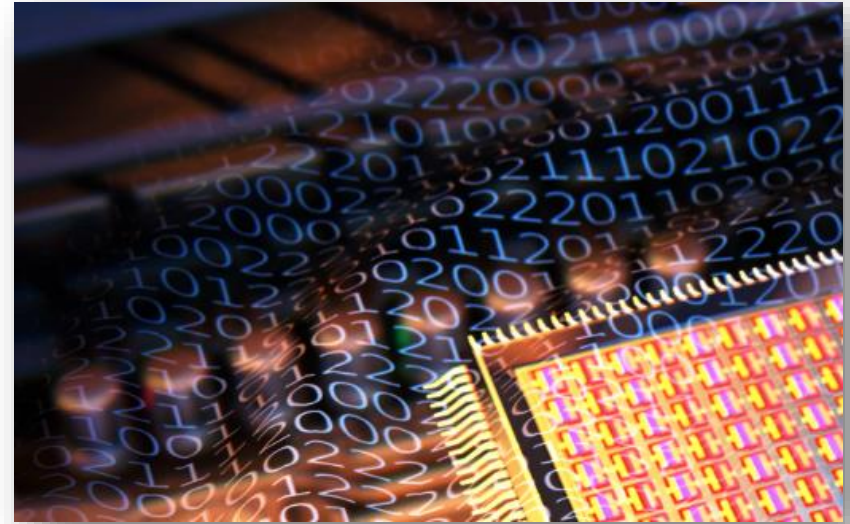


Multi-valued Logic

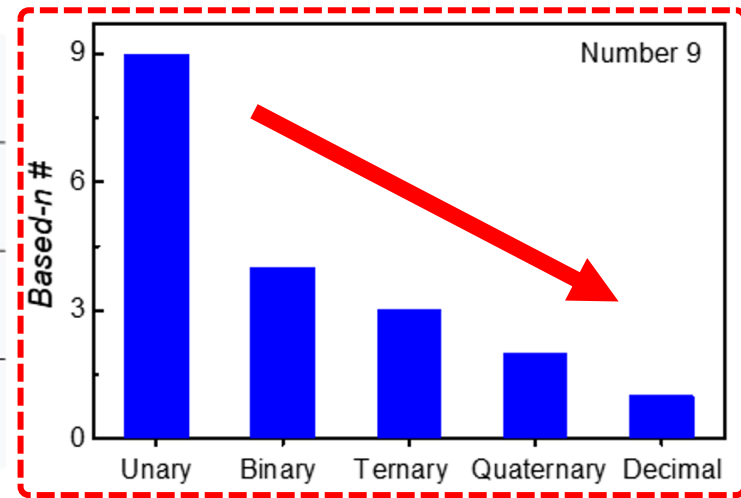
Binary



Ternary



Decimal	1	2	3	4	5	6	7	8	9
Binary	1	10	11	100	101	110	111	1000	1001
Ternary	1	2	10	11	12	20	21	22	100
Quaternary	1	2	3	10	11	12	13	20	21

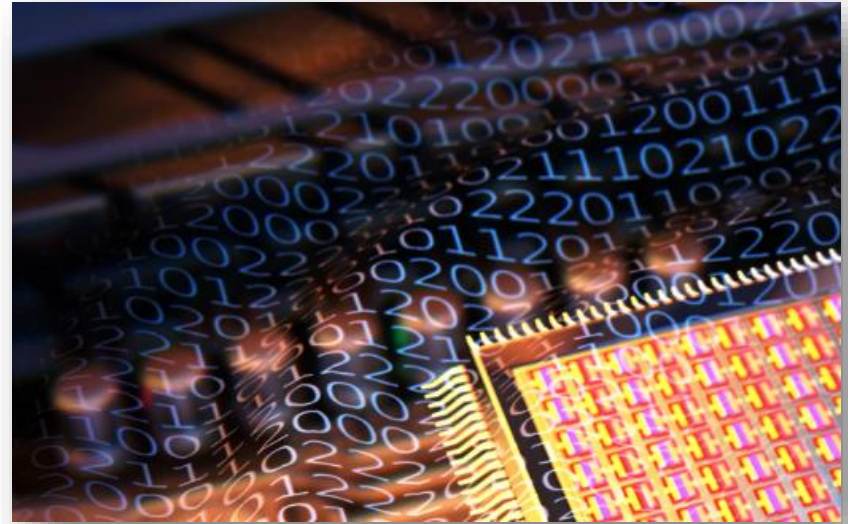


Multi-valued Logic

Binary



Ternary



Higher Information
Density



Reduced interconnect
Lines

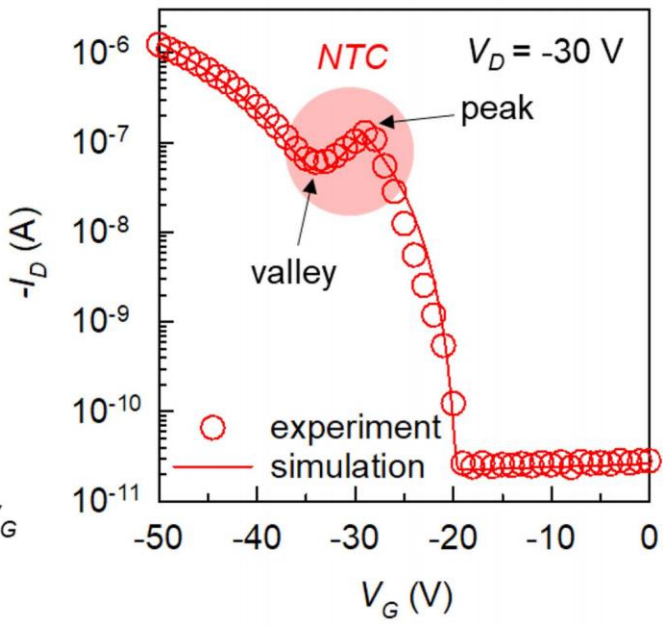
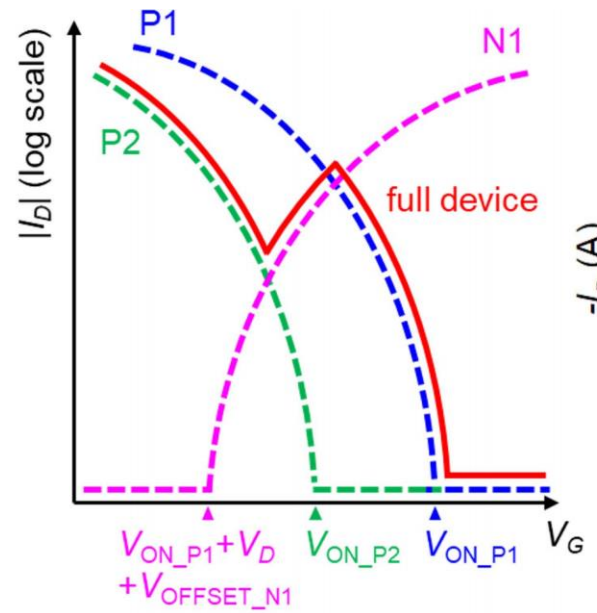
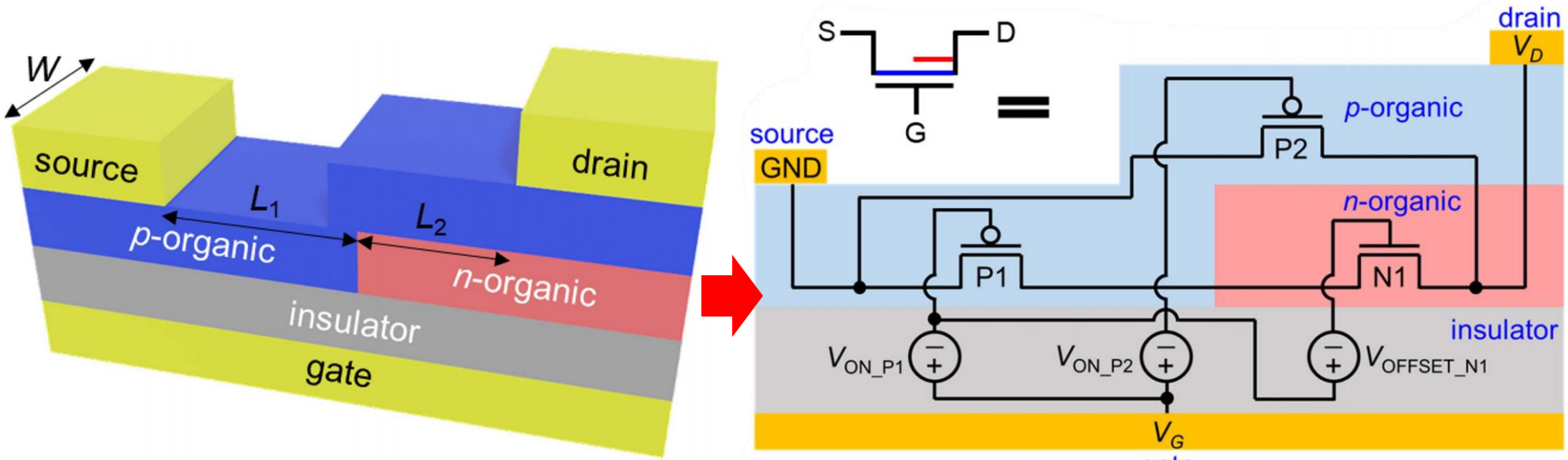


Lower Power
Consumption



How to make ternary logic?

Multi-valued Logic



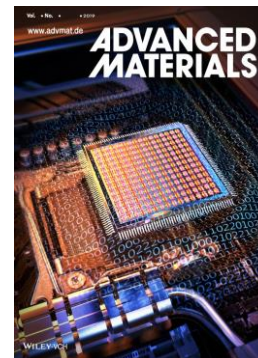
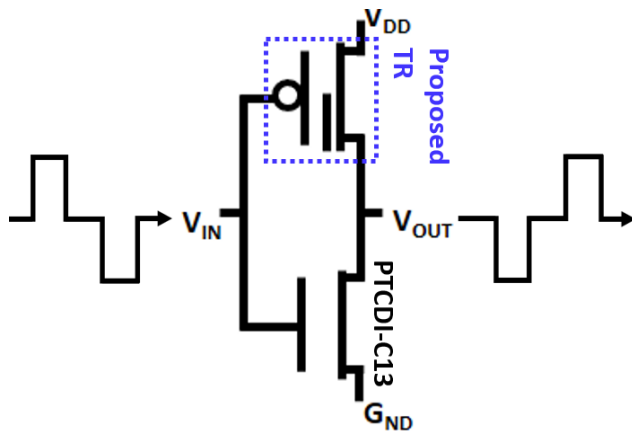
- Peak/valley current
- NTC region
- Well-defined off-current
- Well-defined on-current

Multi-valued Logic

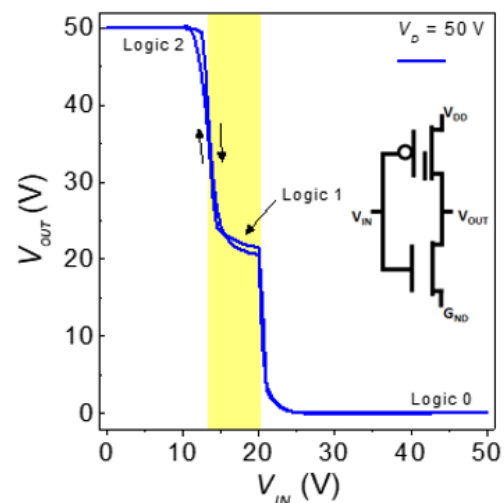
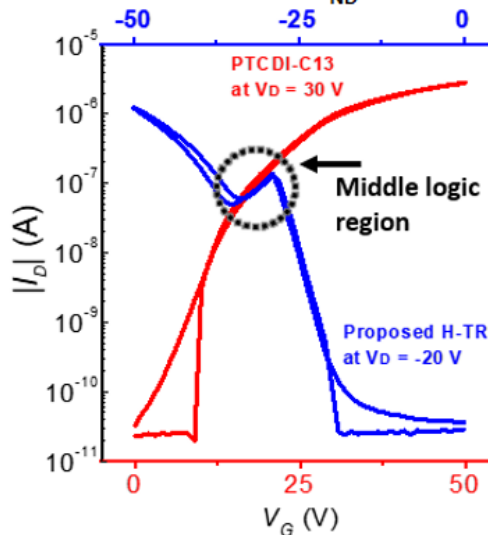
Logic = 2 (V_{DD}) \rightarrow Logic = 1 ($V_{DD}/2$) \rightarrow Logic = 0 (G_{ND})

DC
characteristic

Transient
characteristic



Front cover, July 2019

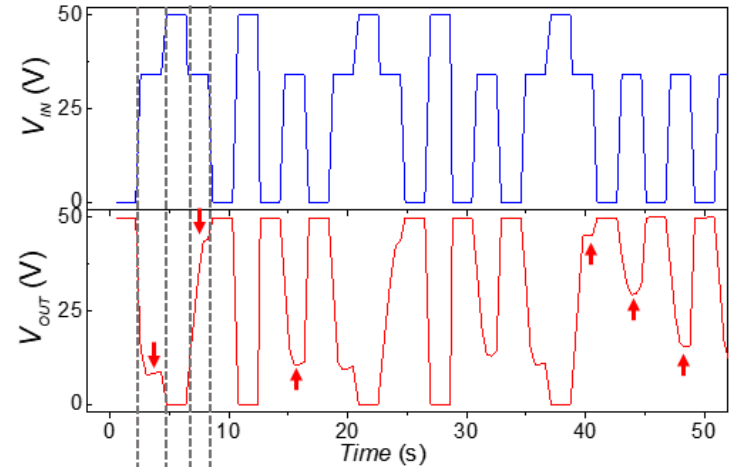
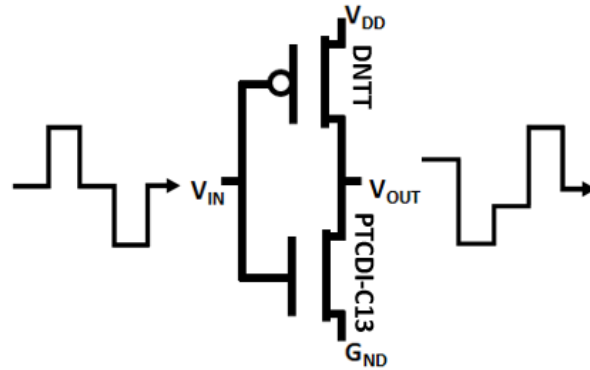


☺ Three logic state (Logic = 2, 1, 0)

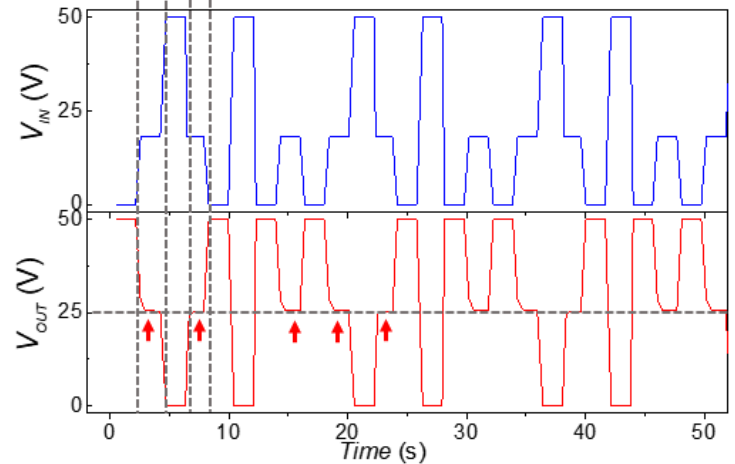
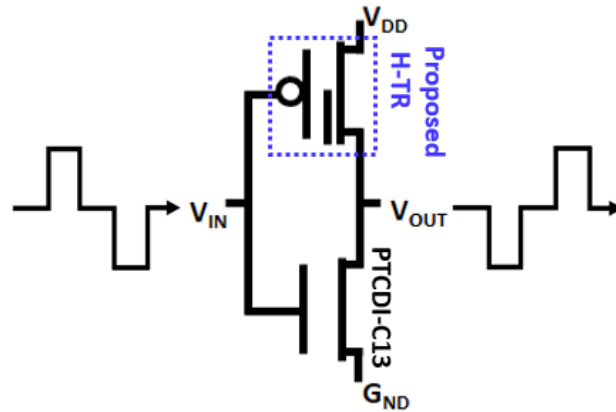
Multi-valued Logic

Logic = 2 (V_{DD}) \rightarrow Logic = 1 ($V_{DD}/2$) \rightarrow Logic = 0 (G_{ND})

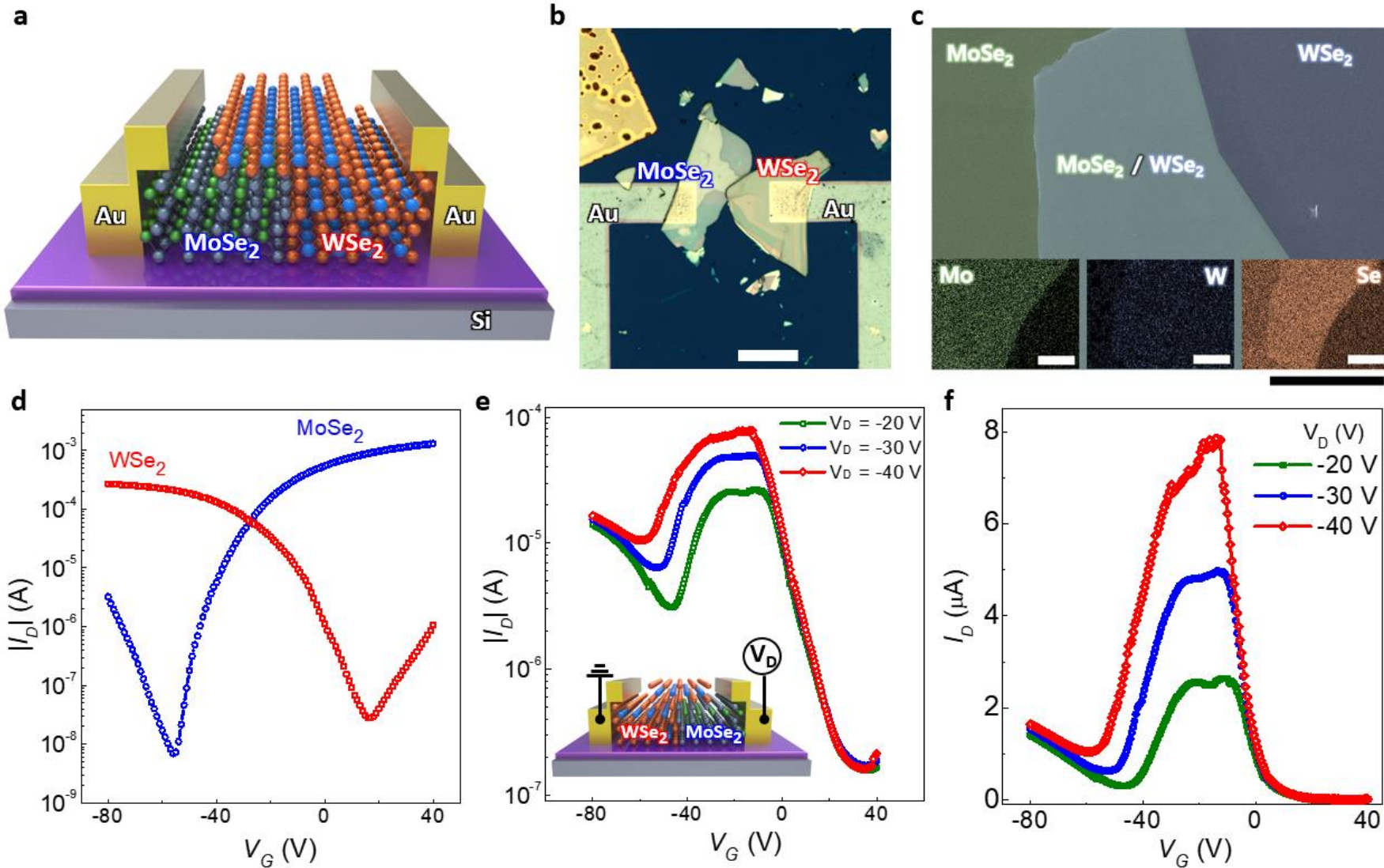
DC
characteristic



Transient
characteristic



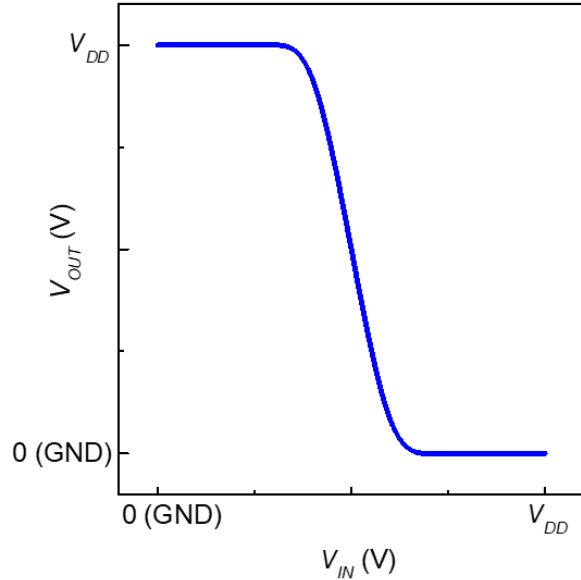
Multi-valued Logic



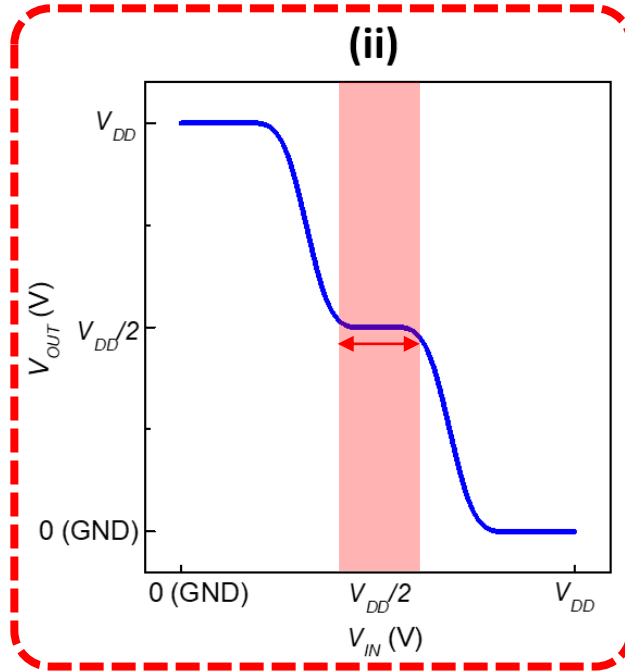
Unpublished results

Multi-valued Logic

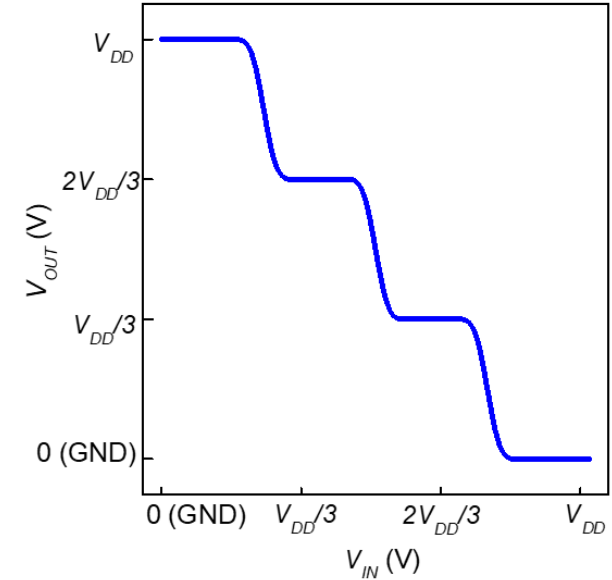
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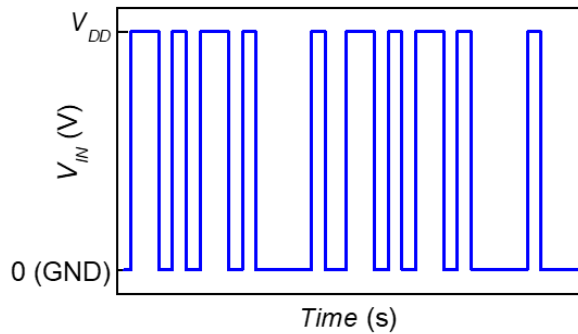
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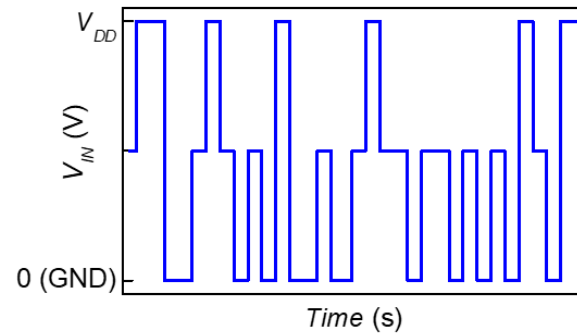
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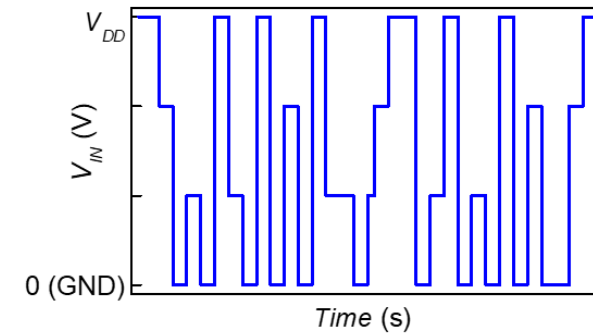
(i)



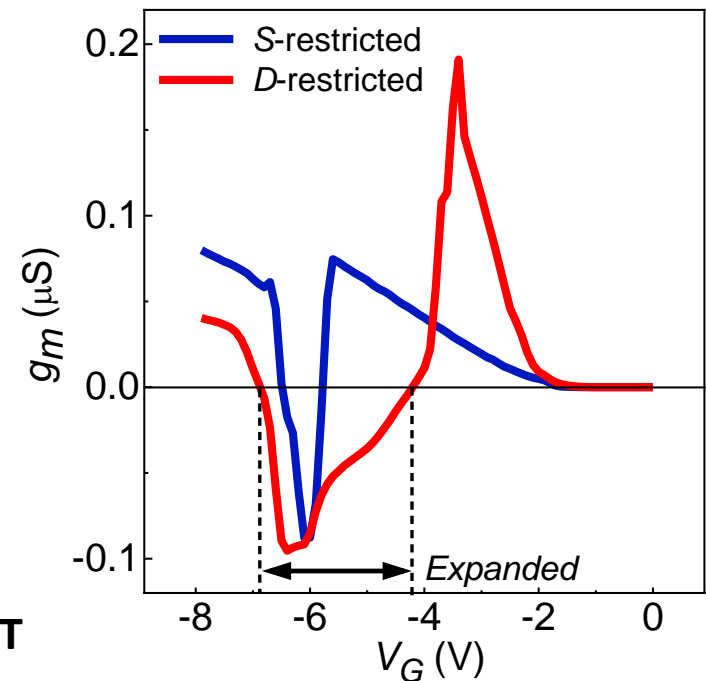
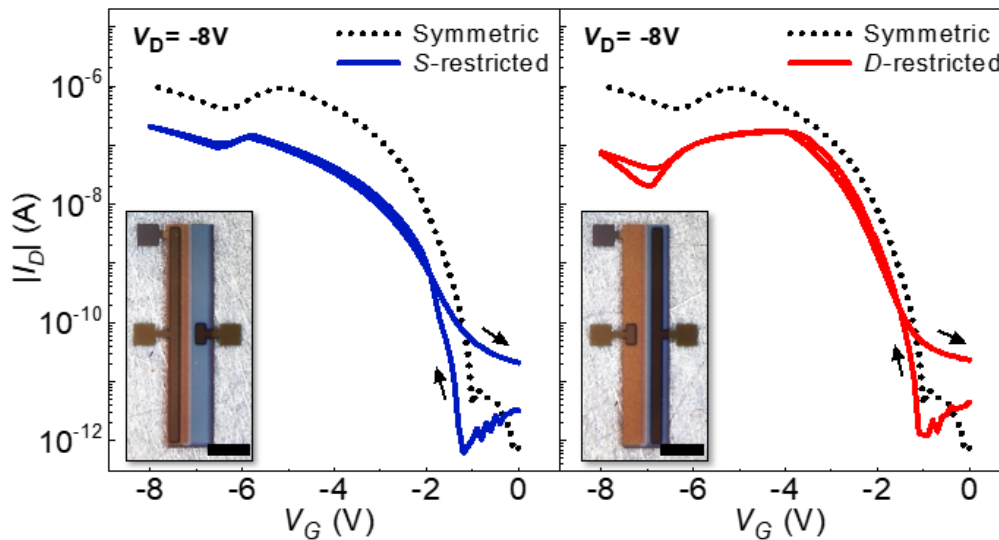
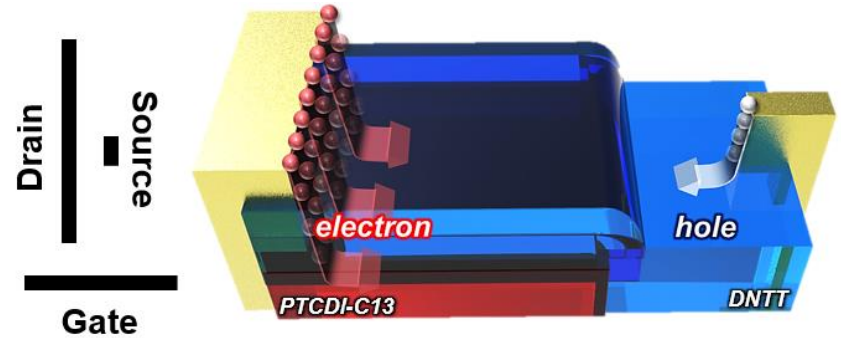
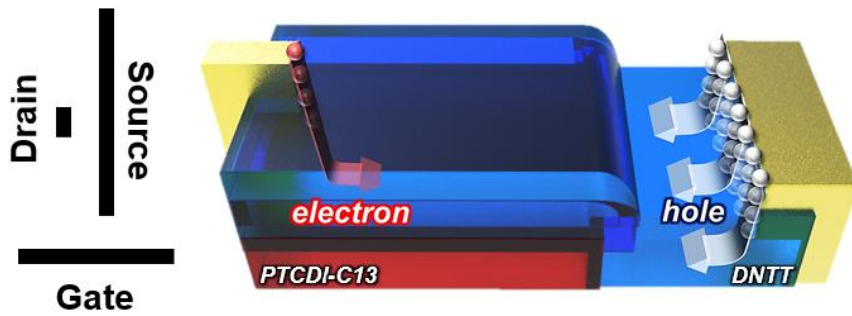
(ii)



(iii)



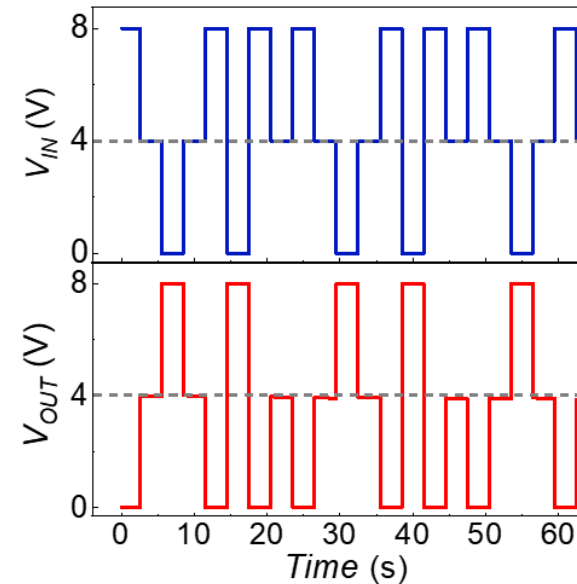
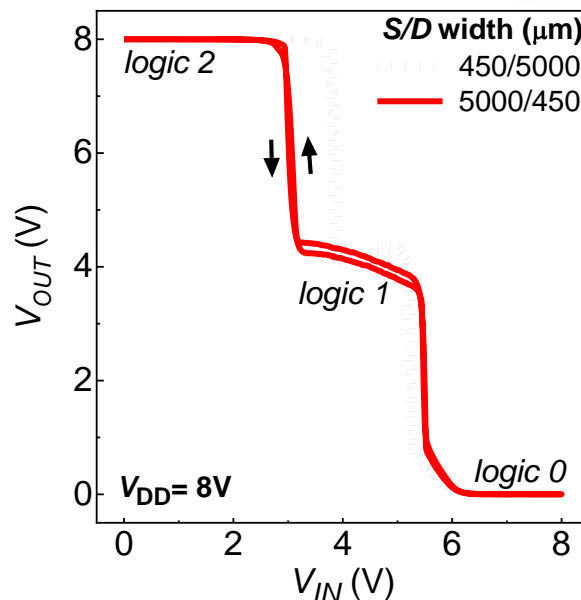
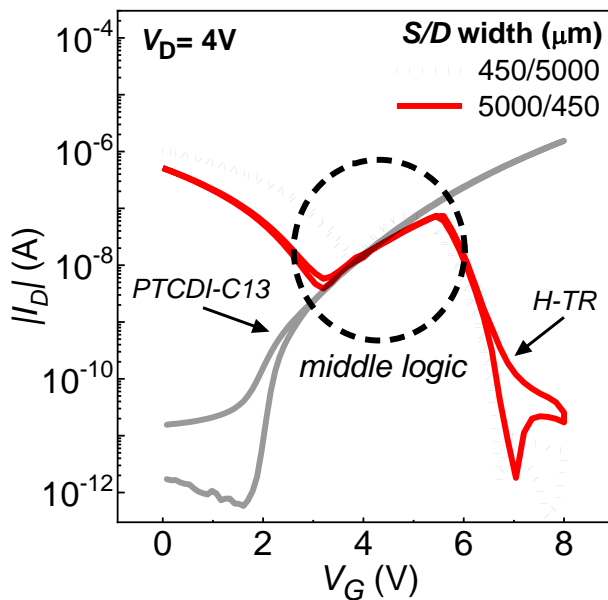
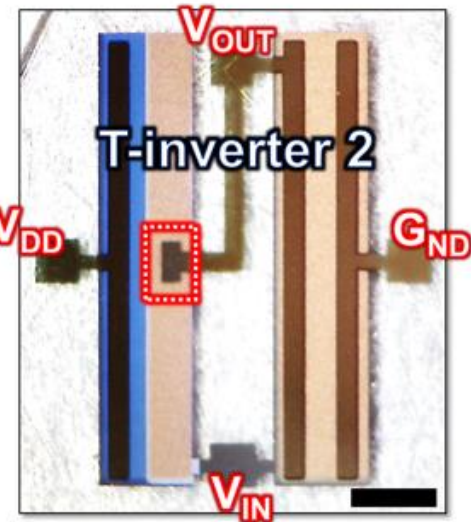
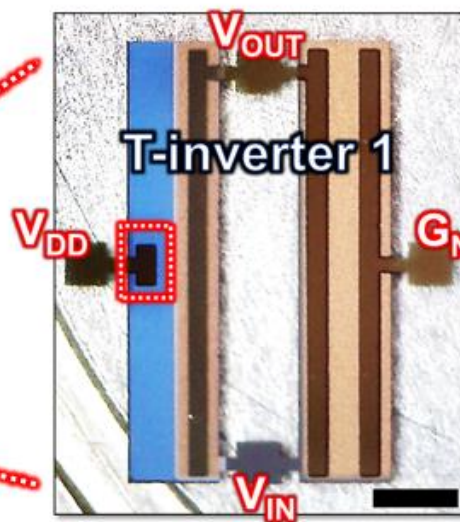
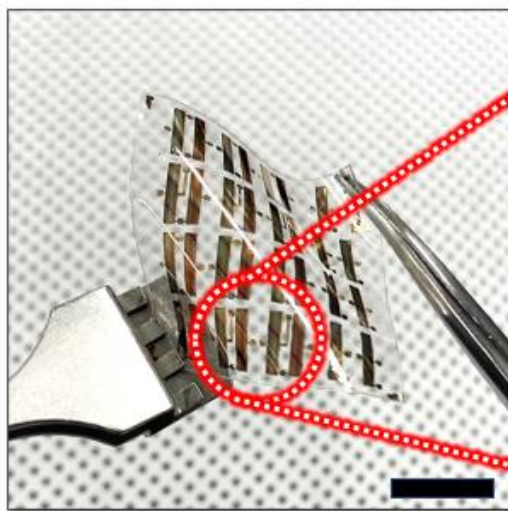
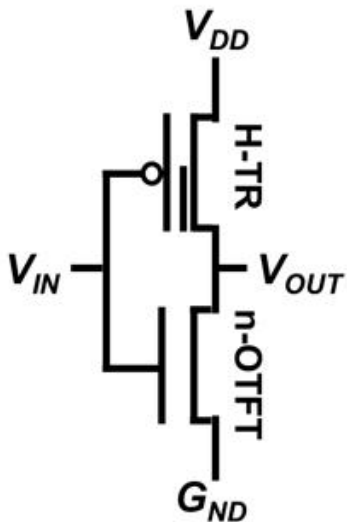
NDT ternary circuits



☺ Asymmetric metal width scheme → Control of NDT

☺ Larger NDT ↔ Shorter NDT depending on the metal width ratio

NDT ternary circuits

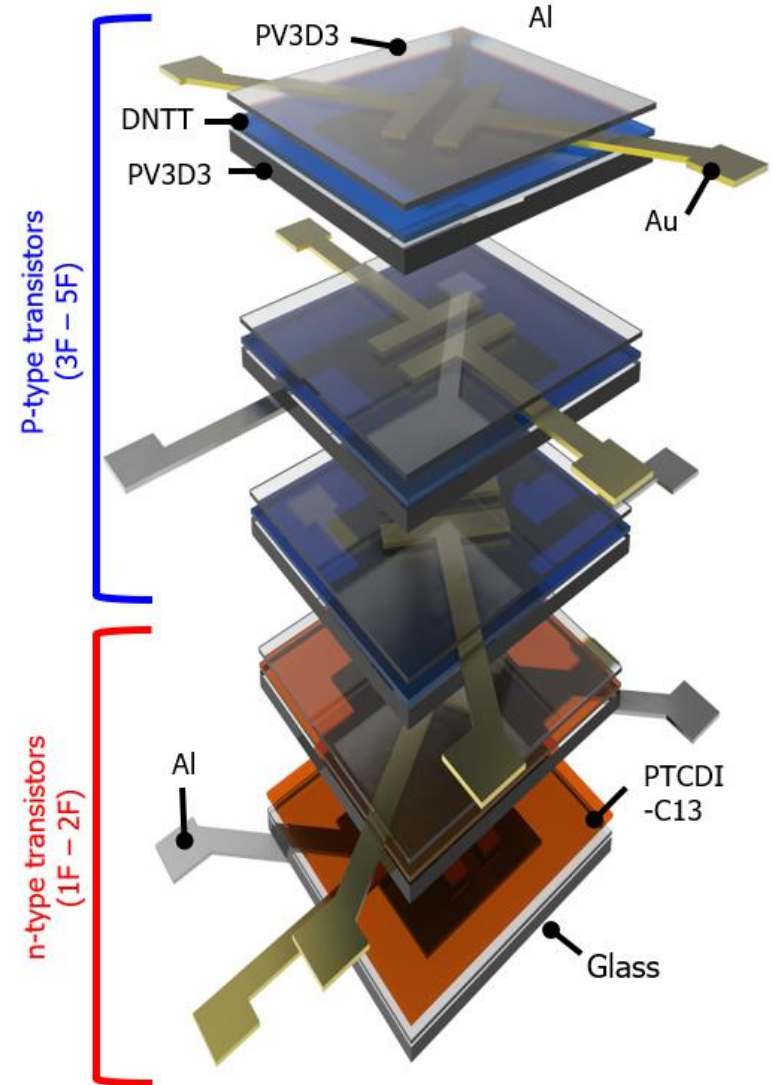
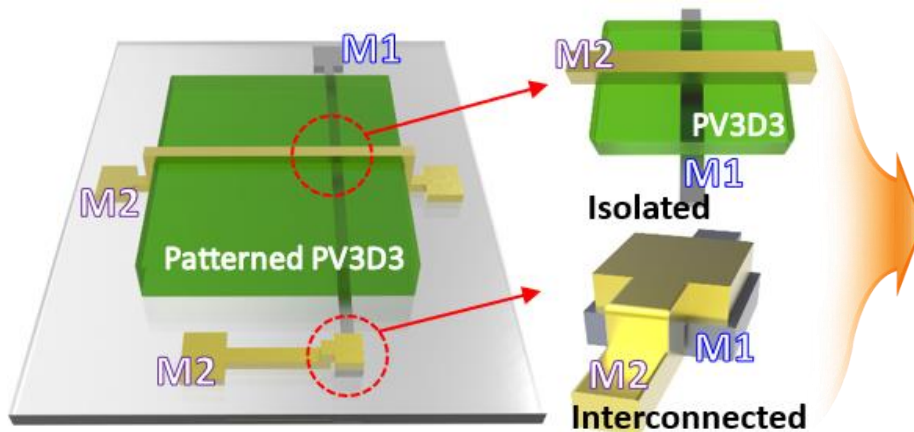


Flexible ternary circuits using asymmetric metal width transistors

Chungryul Lee, Hocheon Yoo *et al.*, *Small* (2021)

Via-Hole-Less Metal Interconnects

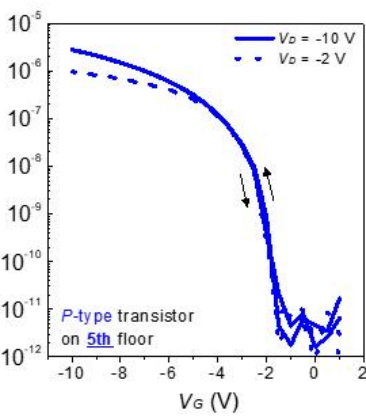
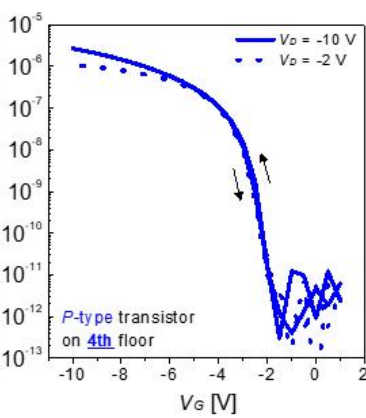
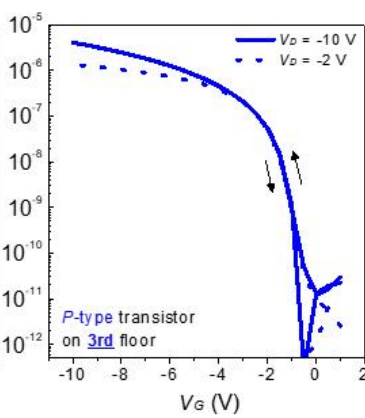
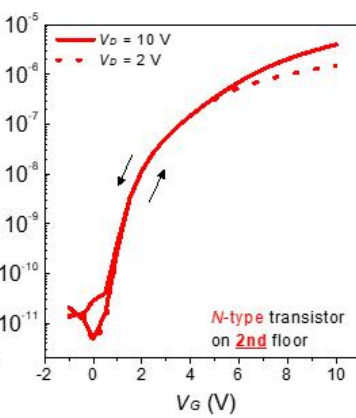
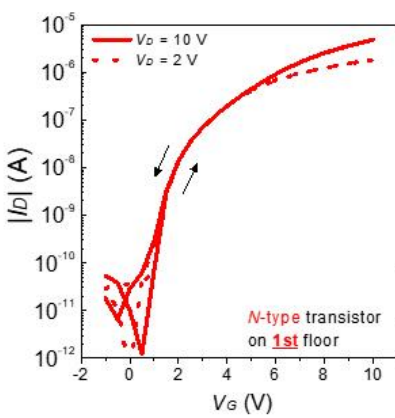
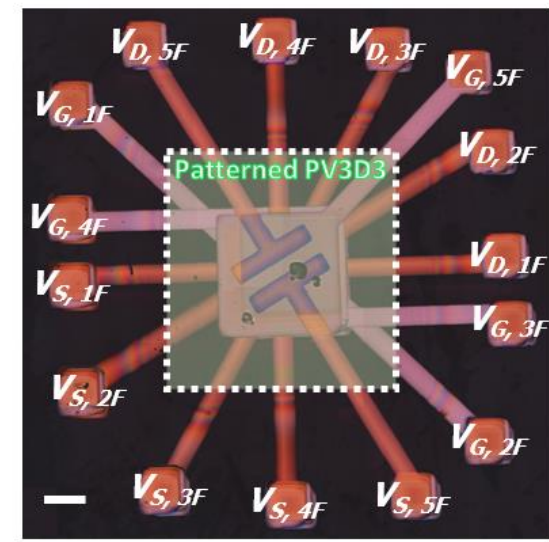
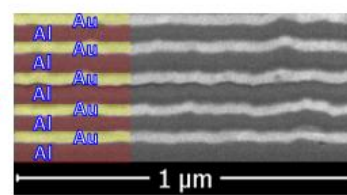
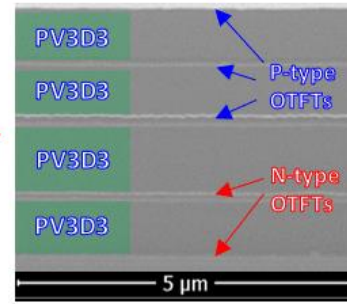
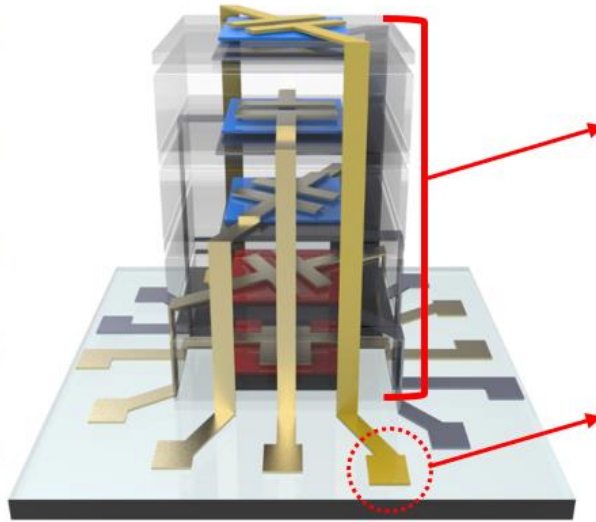
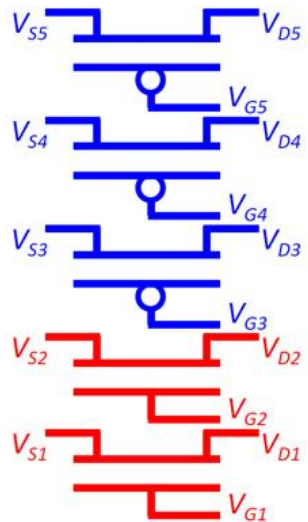
Via-hole-less integration scheme



- ☺ Etching-free multilevel metal interconnect
- ☺ Solvent-free multilevel metal interconnect
- ☺ Simultaneous interconnection formation

Hocheon Yoo, Hongkeun Park *et al.*, *IEEE Electron Device Letters* In progress
Hocheon Yoo, Hongkeun Park *et al.*, *Nature Communications* (2019) 10, 2424.

Via-Hole-Less Metal Interconnects



😊 100% Yield

😊 5-time higher density of devices

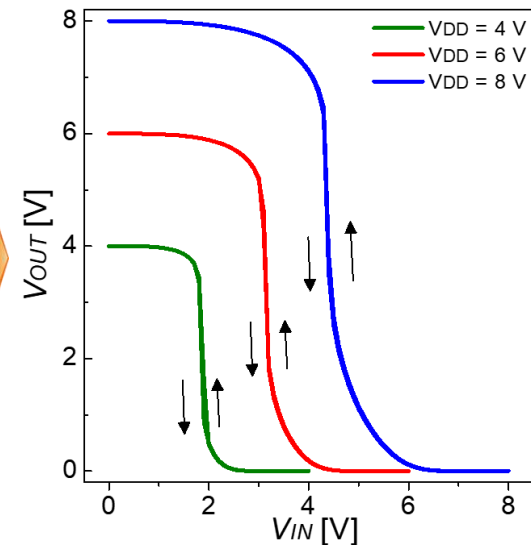
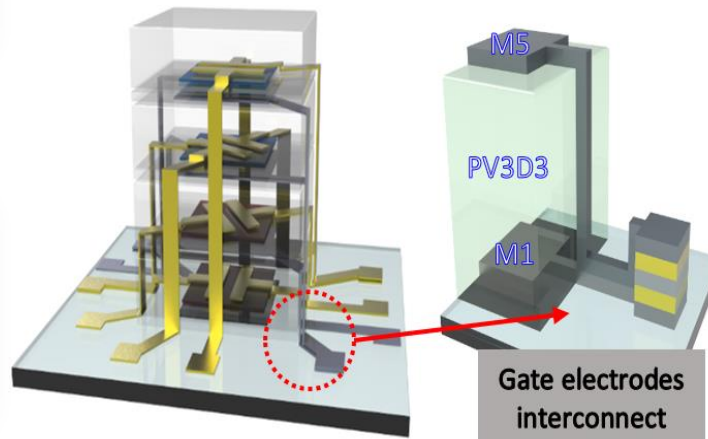
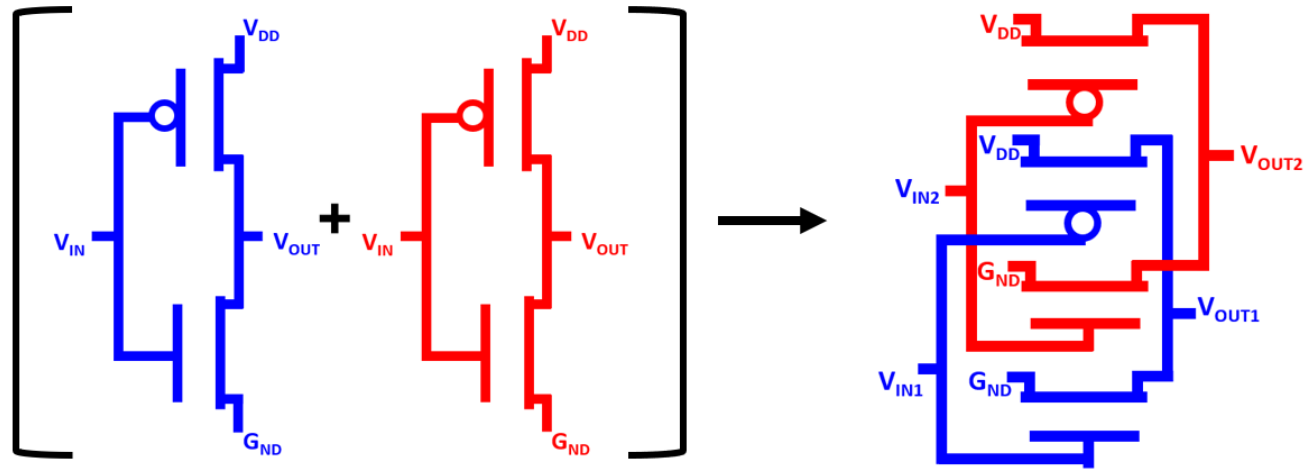
Highlighted in *Nature Research Device & Materials Engineering Community*

Via-Hole-Less Metal Interconnects

3D-Integrated
Inverter Circuit

3D-Integrated
NAND/NOR
Circuit

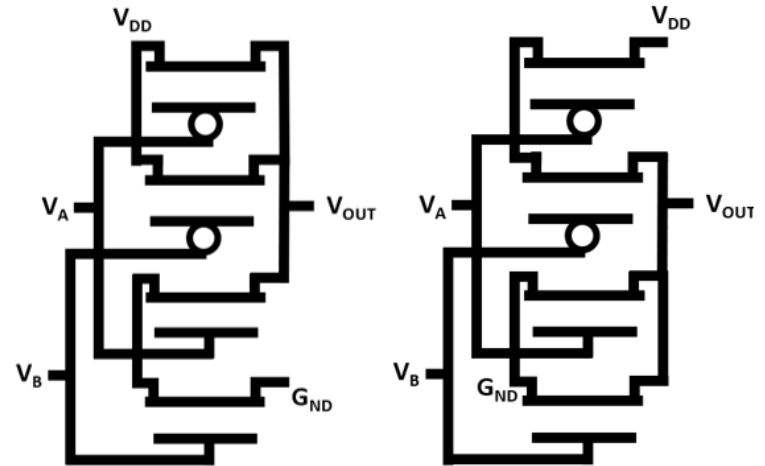
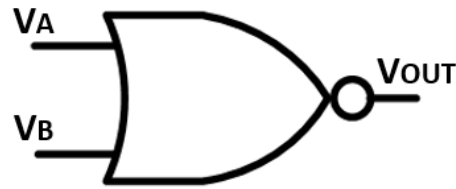
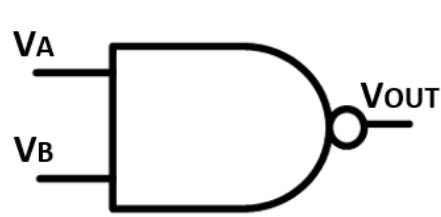
Exclusive OR
Circuit



Hocheon Yoo, Hongkeun Park *et al.*, *Nature Communications* (2019) 10, 2424
Highlighted in *Nature Research Device & Materials Engineering Community*

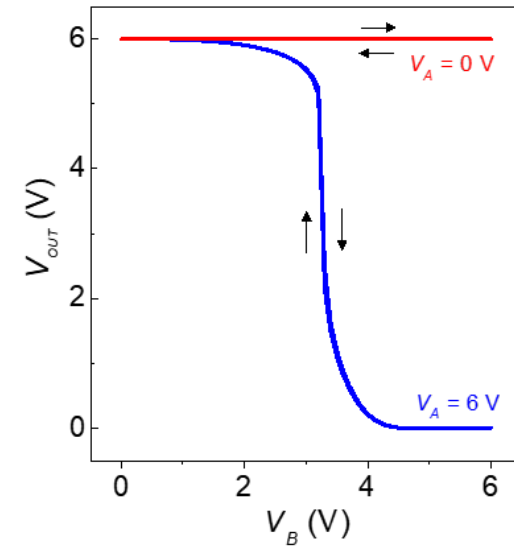
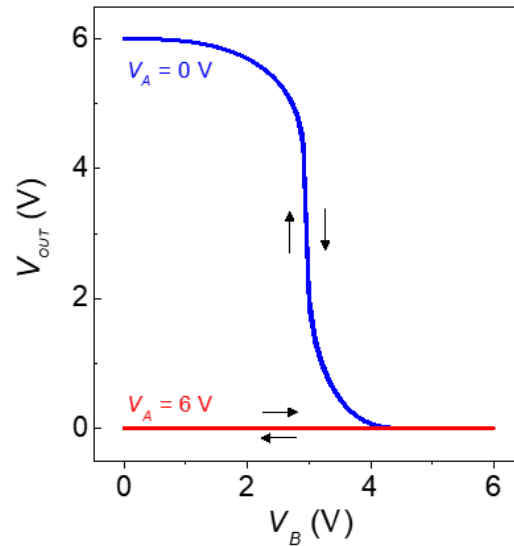
Via-Hole-Less Metal Interconnects

3D-Integrated
Inverter Circuit



3D-Integrated
NAND/NOR
Circuit

Exclusive OR
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Hocheon Yoo, Hongkeun Park *et al.*, *IEEE Electron Device Letters*

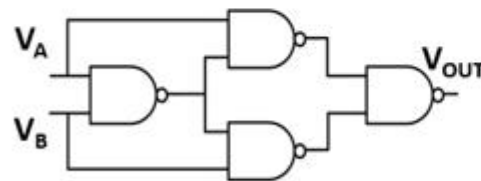
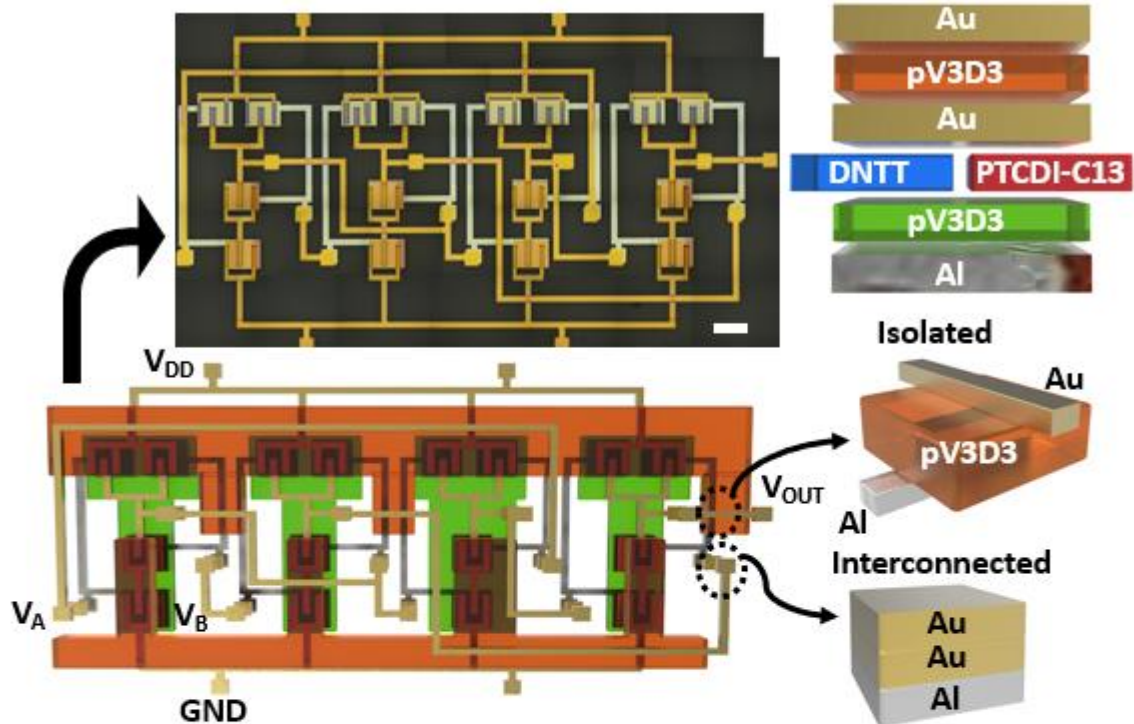
Hocheon Yoo, Hongkeun Park *et al.*, *Nature Communications* (2019) 10, 2424.

Via-Hole-Less Metal Interconnects

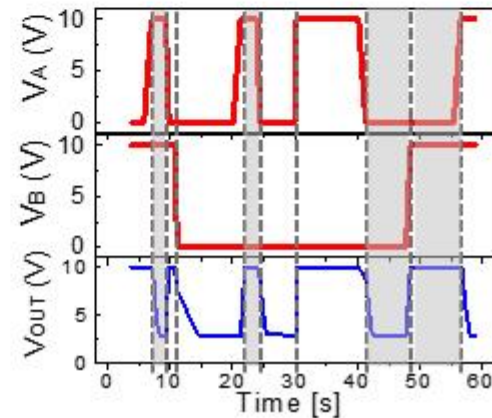
3D-Integrated
Inverter Circuit

3D-Integrated
NAND/NOR
Circuit

Exclusive OR
Circuit



V_A	1	1	0	0
V_B	1	0	0	1
V_{OUT}	0	1	0	1



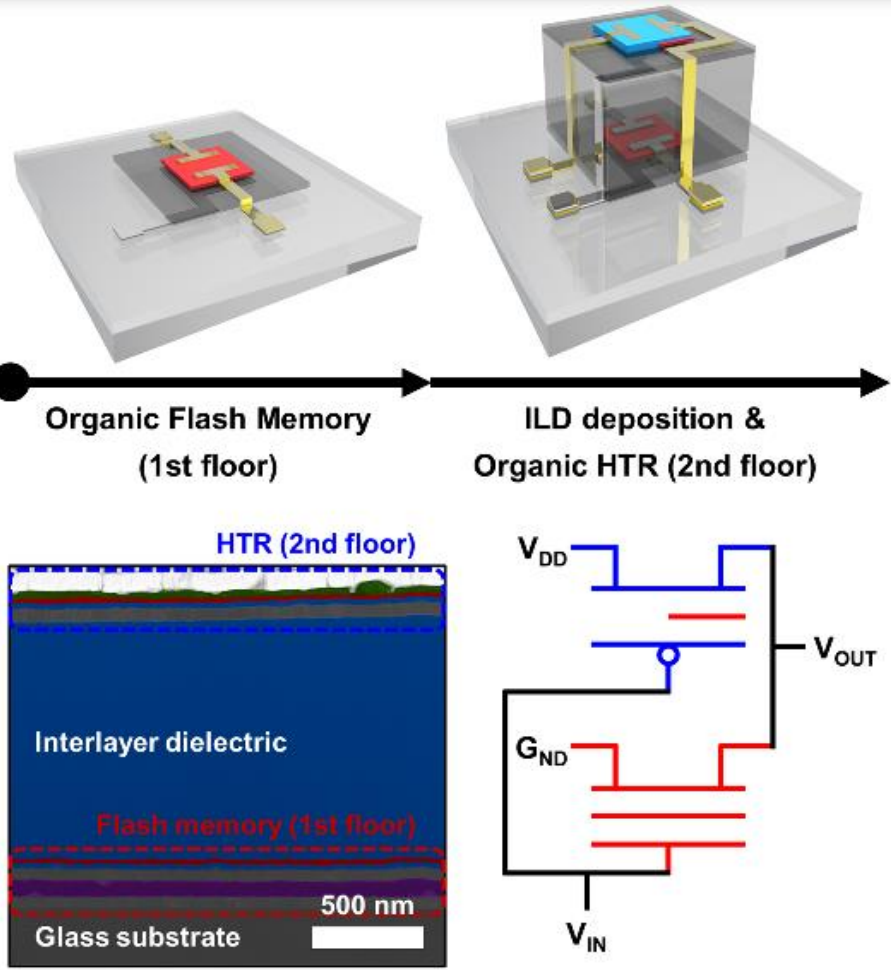
NDT ternary circuits

Vertically-
Integrated MVL

Controllable
MVL operation

MVL depending
on memory states

Vertical 3D Structure



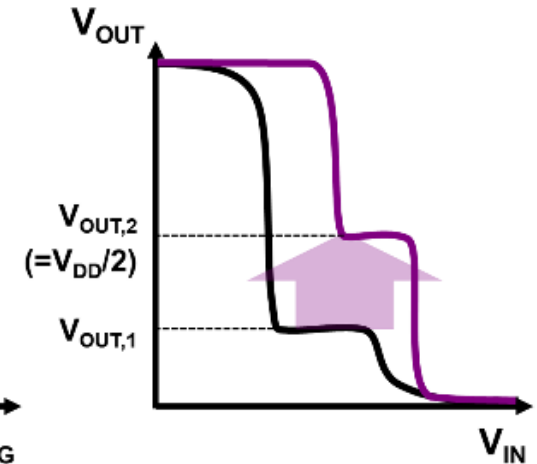
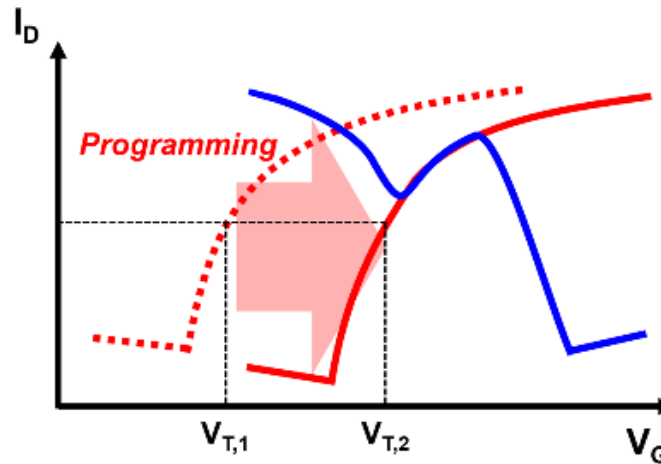
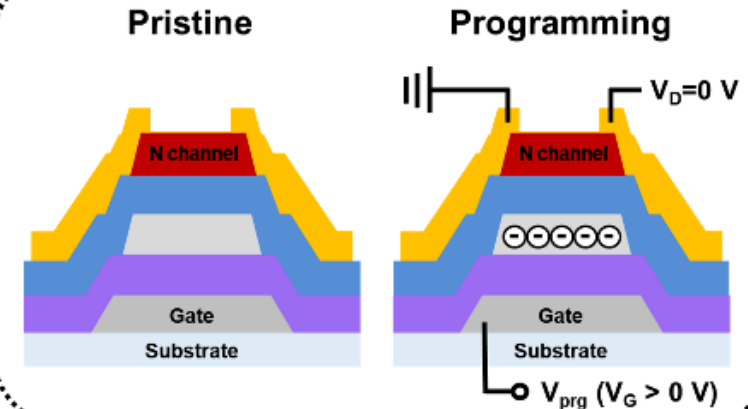
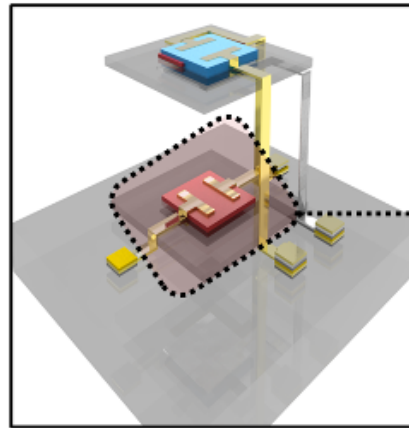
NDT ternary circuits

Vertically-Integrated MVL

Controllable MVL operation

MVL depending on memory states

Introduction of Nonvolatile Flash Memory



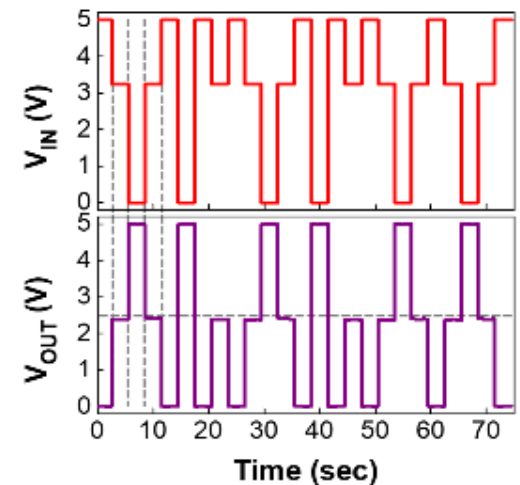
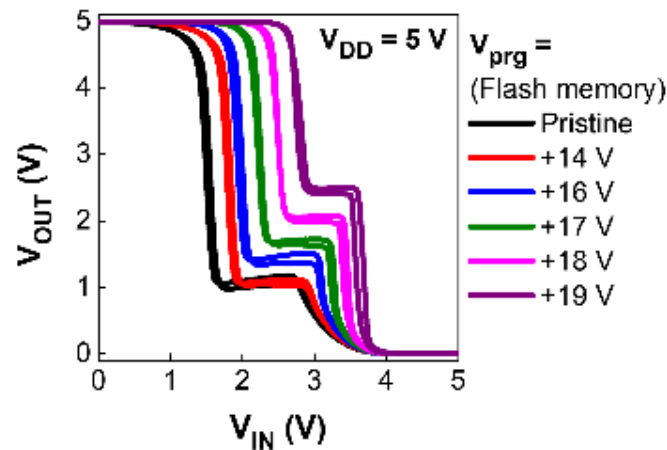
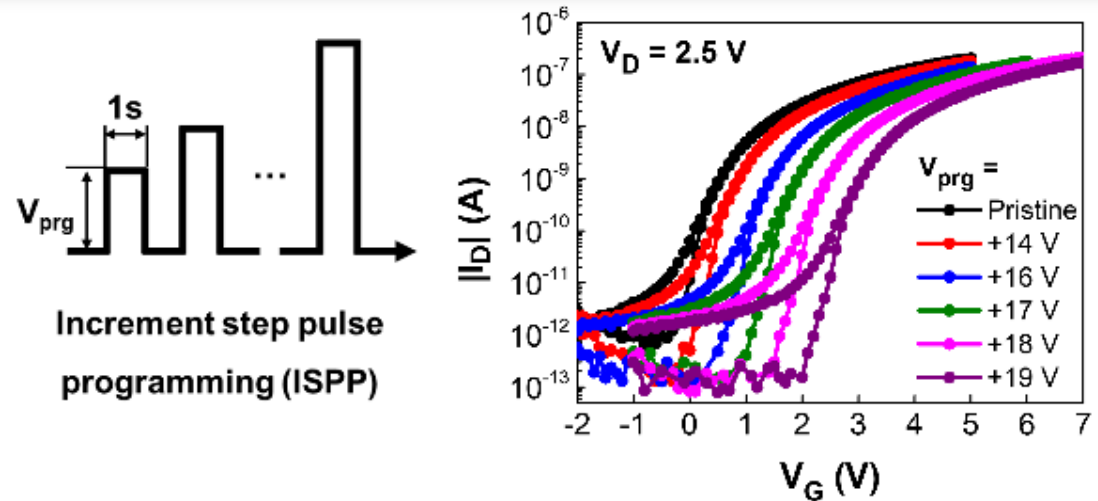
NDT ternary circuits

Vertically-
Integrated MVL

Controllable
MVL operation

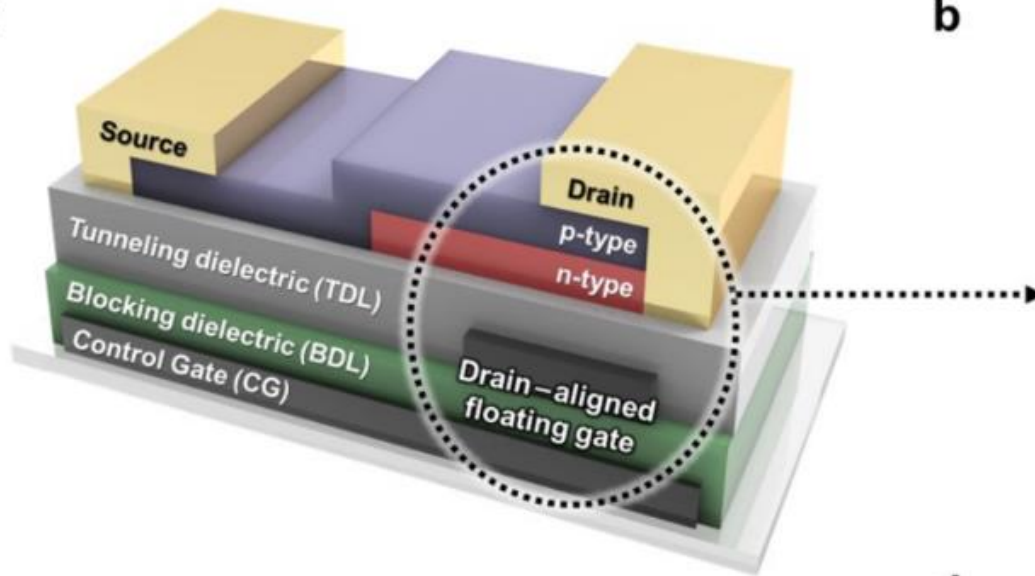
MVL depending
on memory states

Controllable Intermediate Logic State

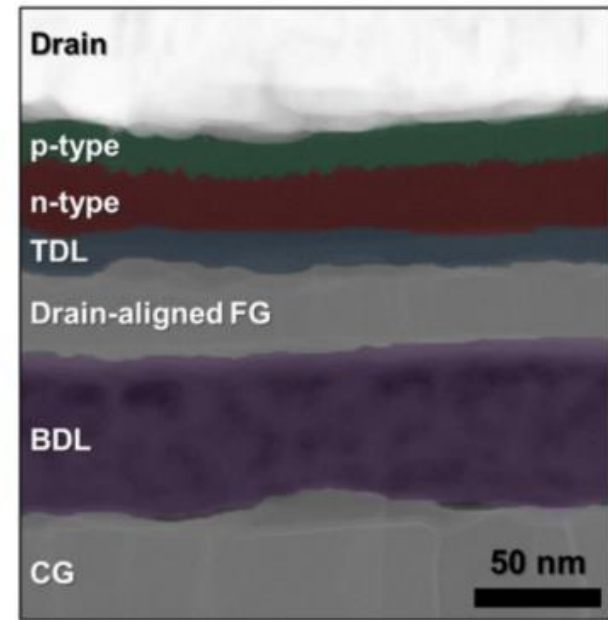


NDT ternary circuits

a

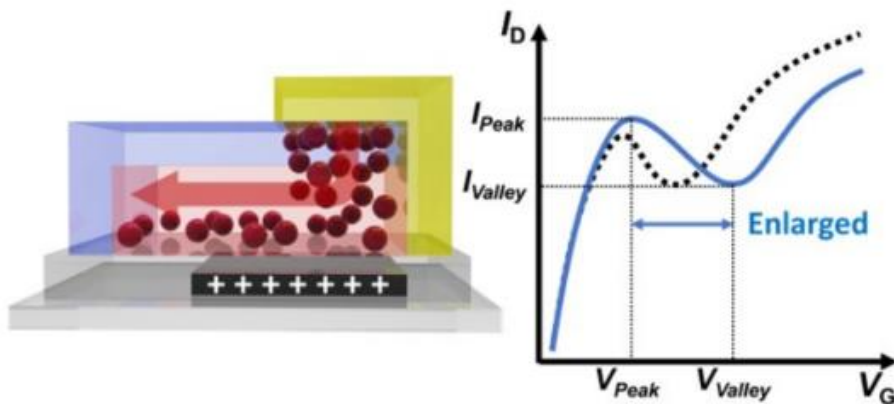


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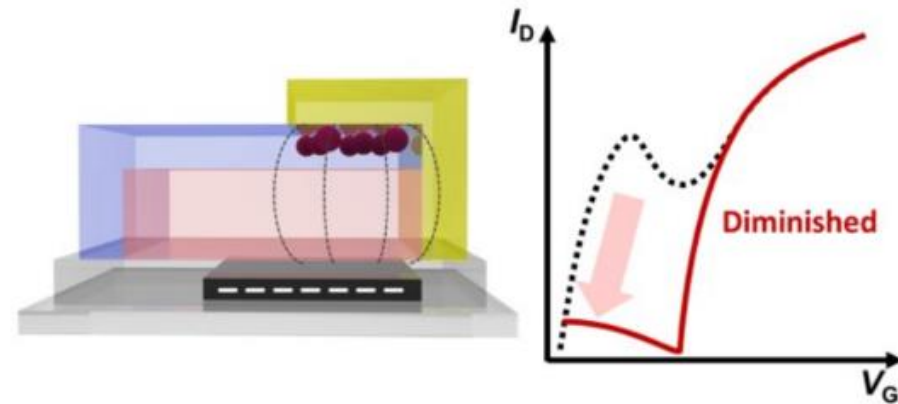


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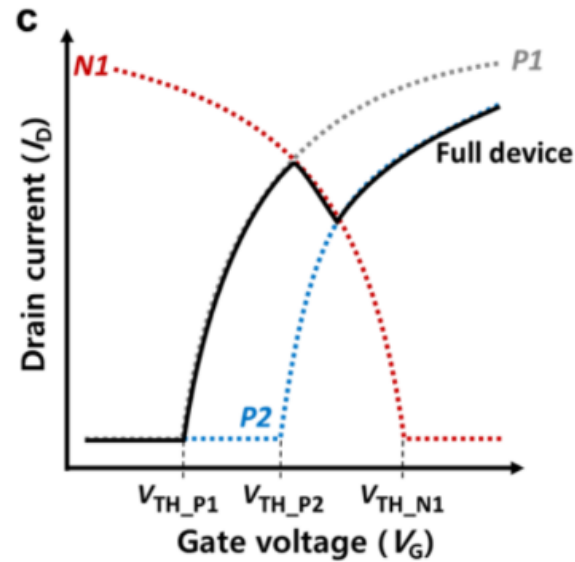
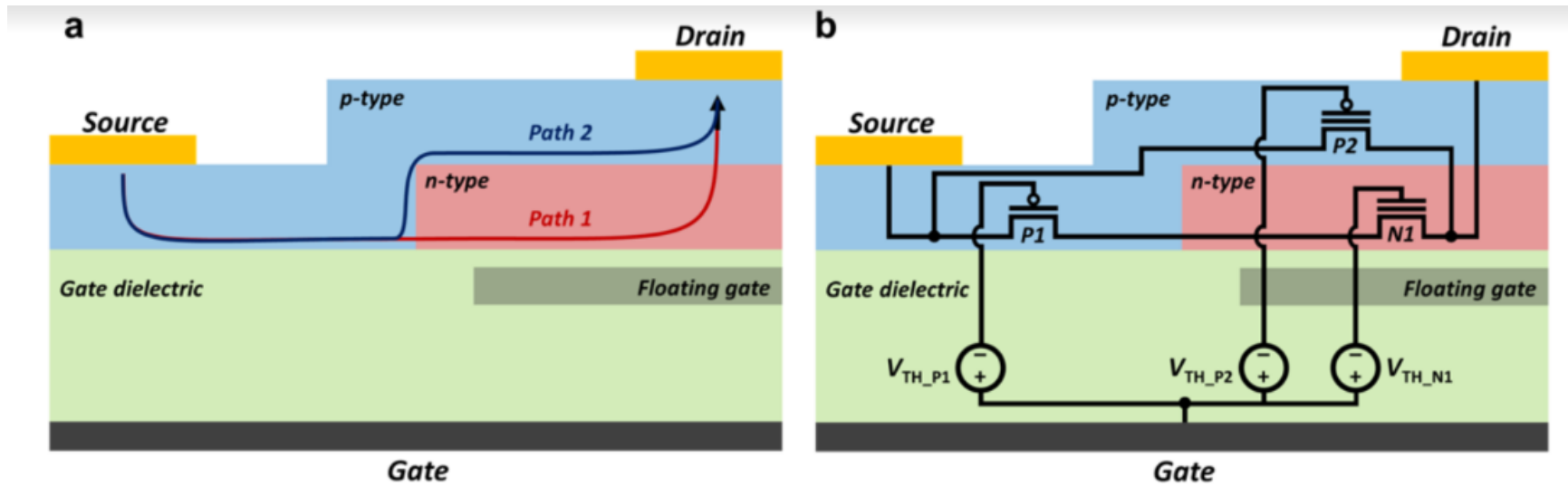
(+) Programmed state: Electron injection \uparrow



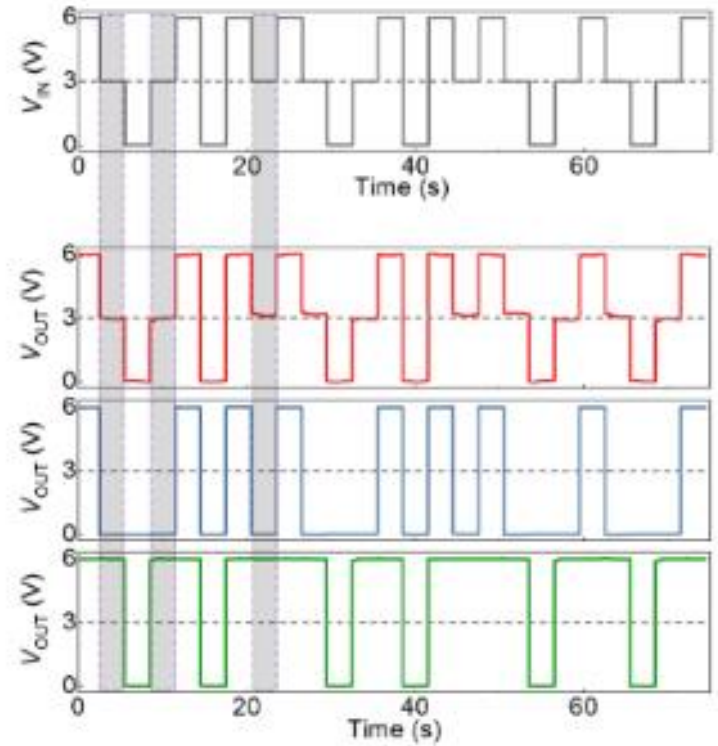
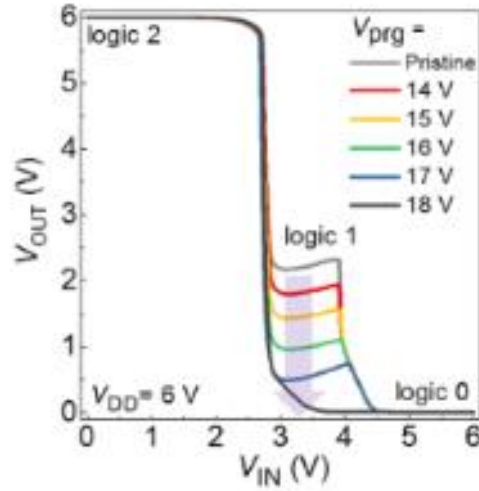
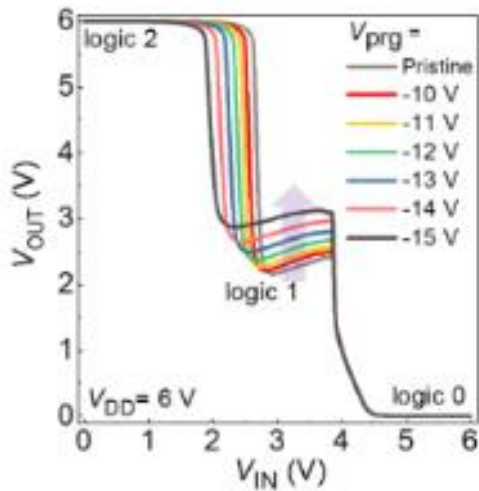
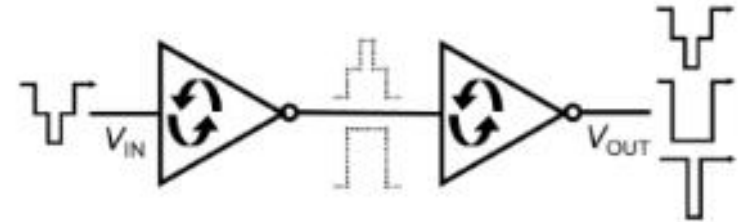
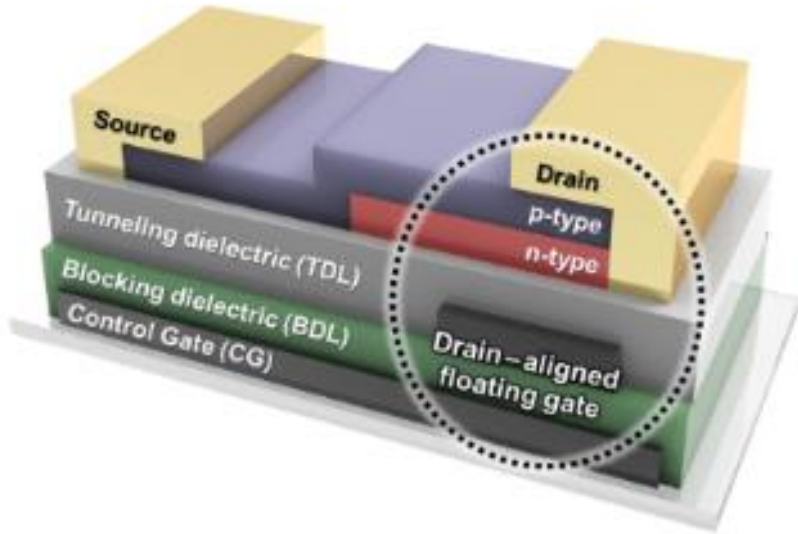
(-) Programmed state: Electron injection \downarrow



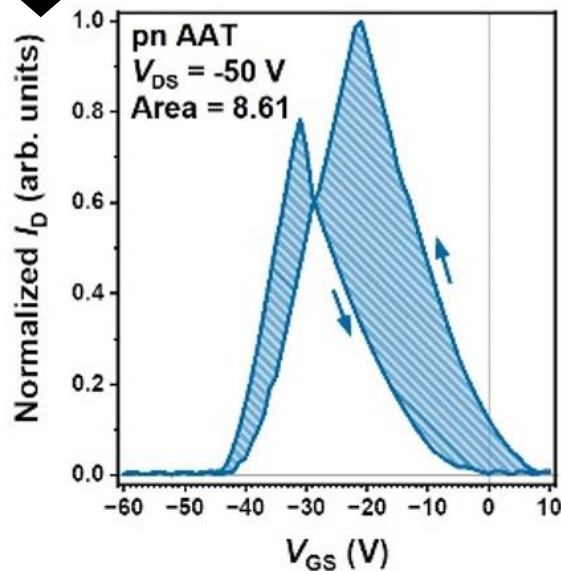
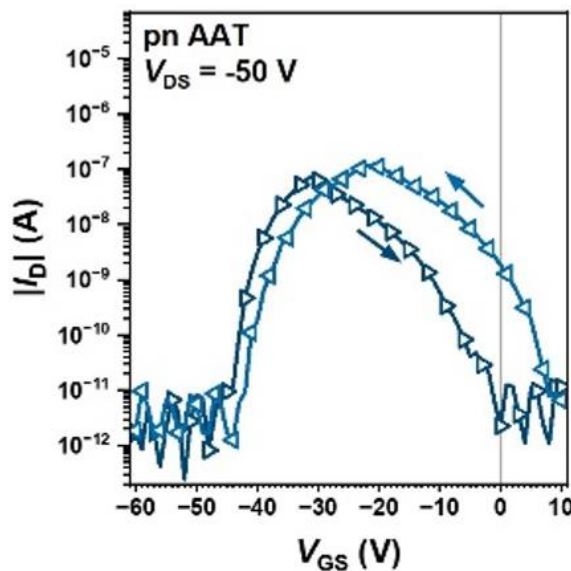
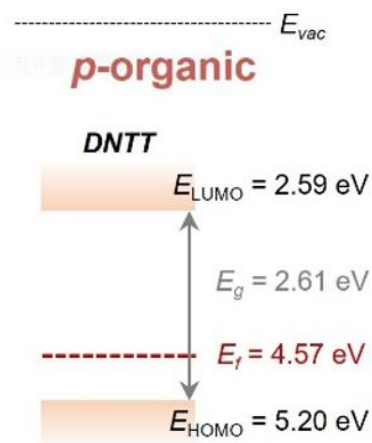
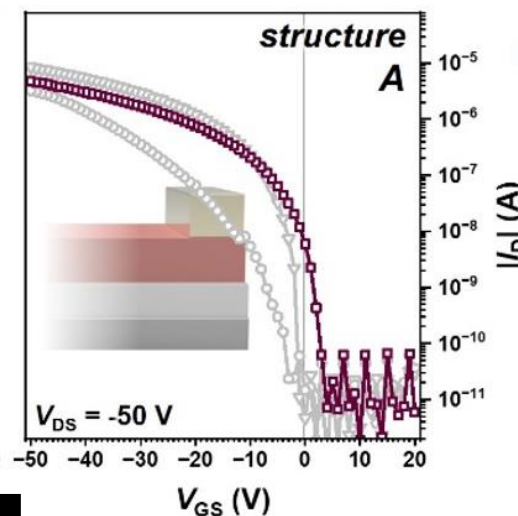
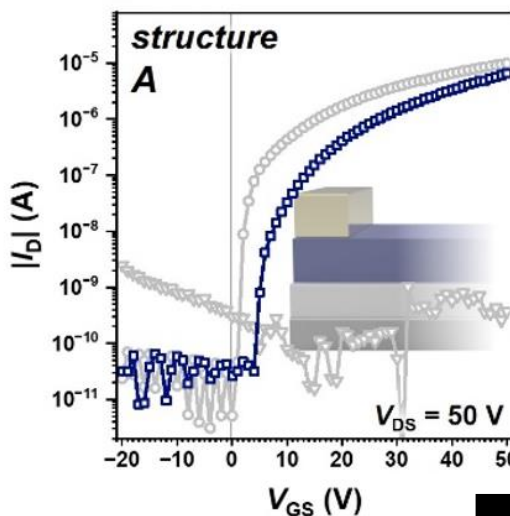
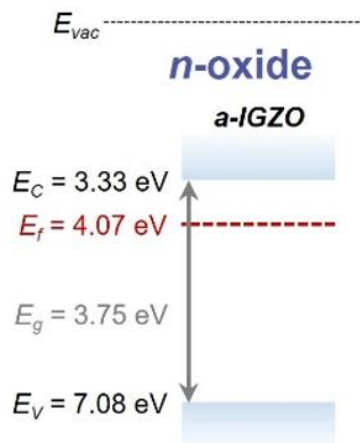
NDT ternary circuits



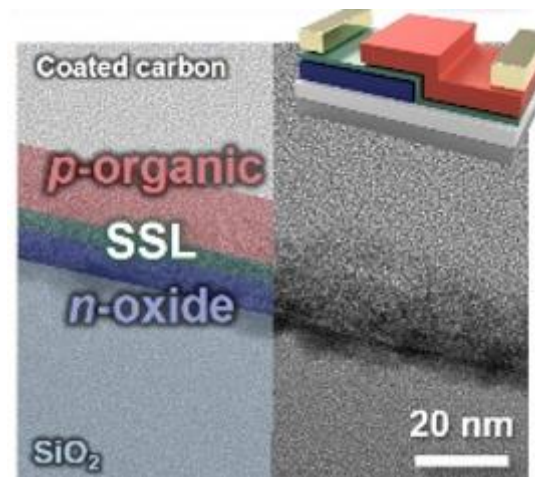
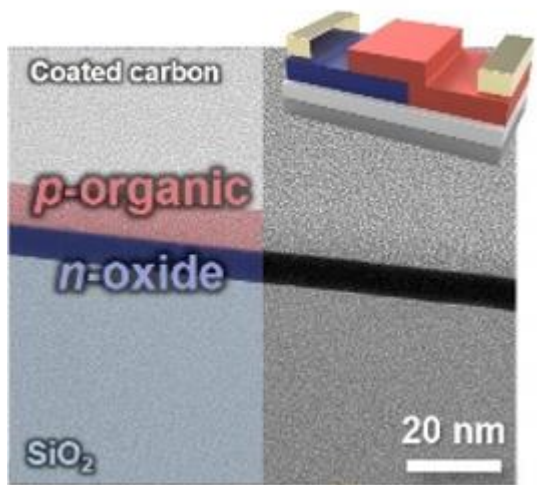
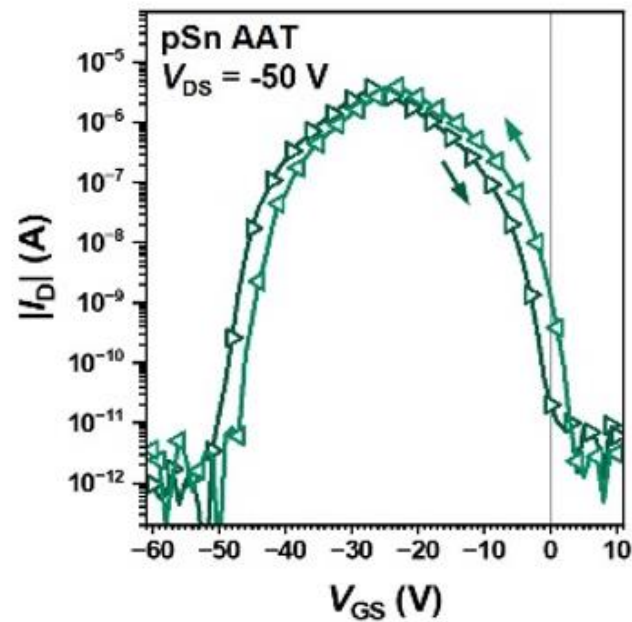
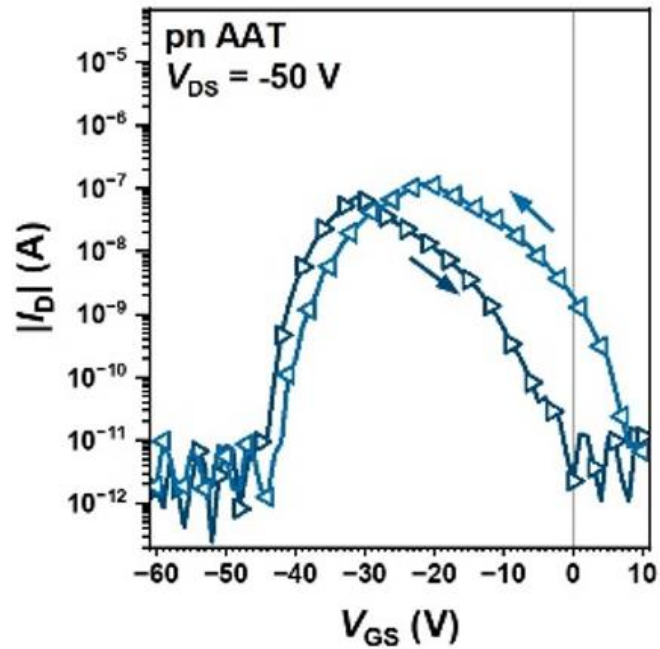
NDT ternary circuits



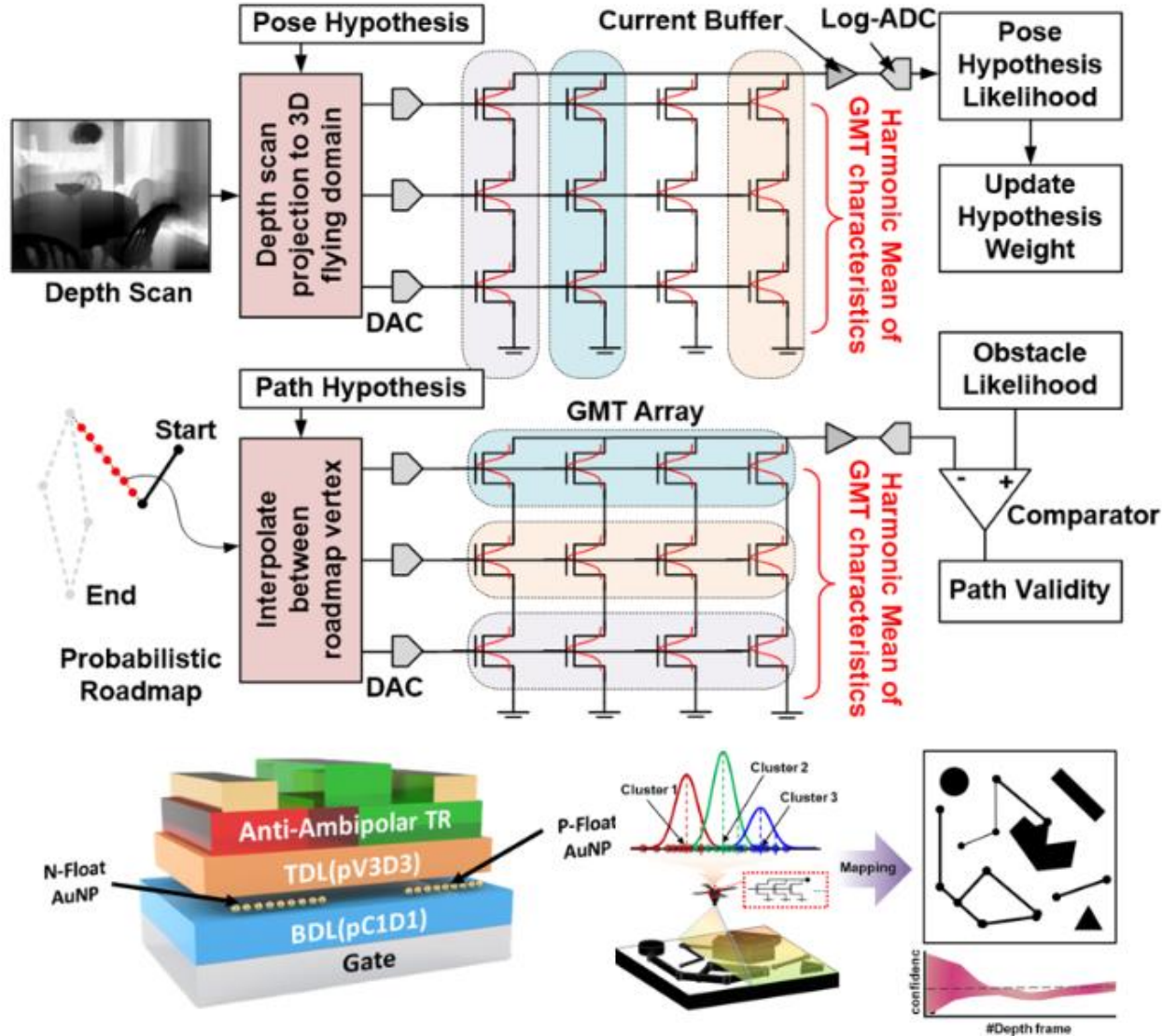
Anti-ambipolar transistors



Anti-ambipolar transistors



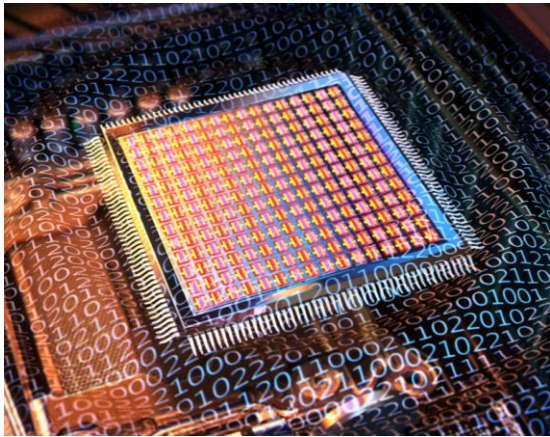
Probabilistic Reasoning with Gaussian Transistors



WHAT'S
NEXT



Multi-valued logic



Security Devices



Physically Unclonable Functions

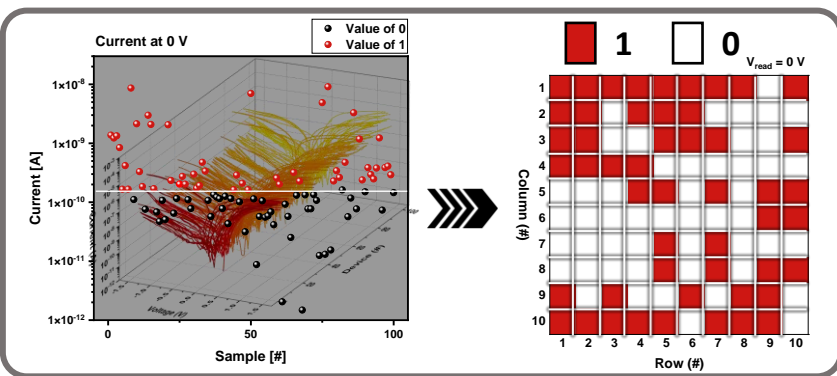
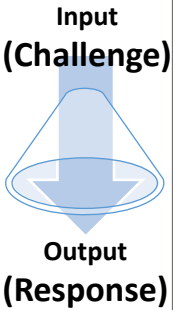
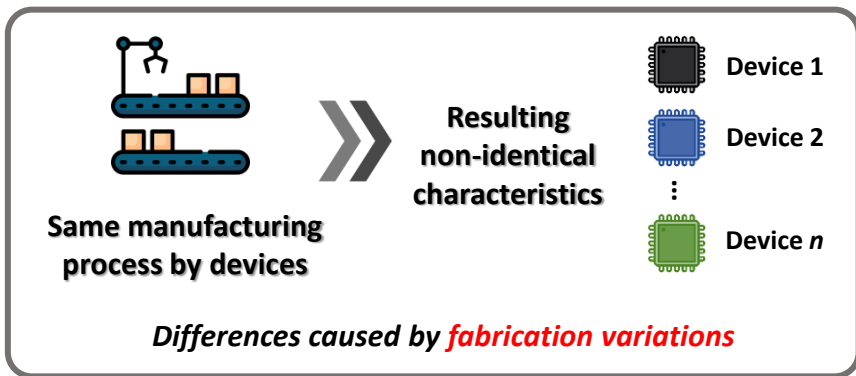


Physically Unclonable Functions

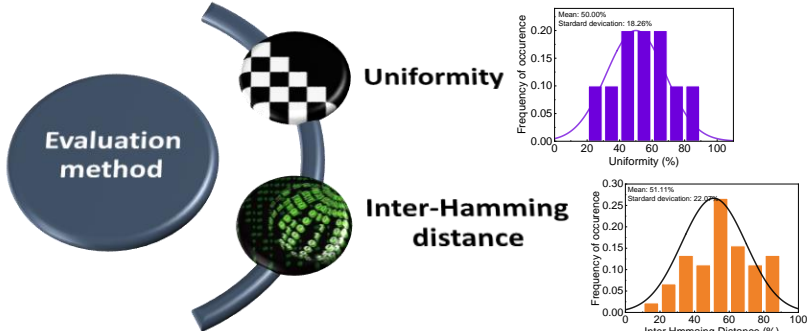


“The only function that cannot be replicated.”

“Digital uniquely identifying fingerprints”



32

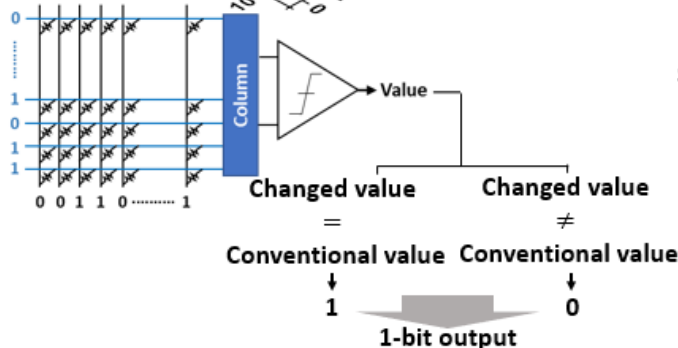
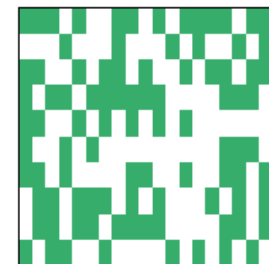
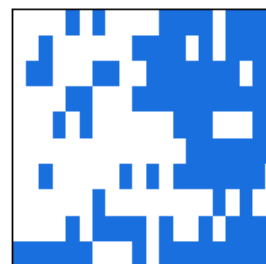
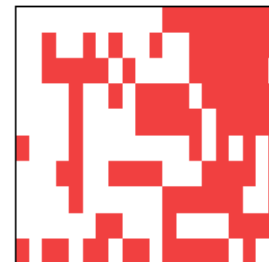
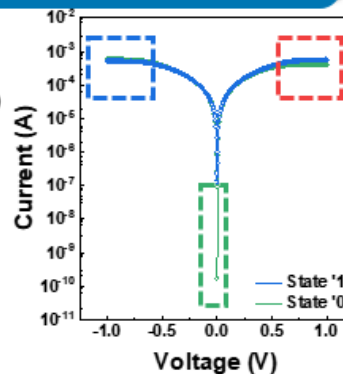
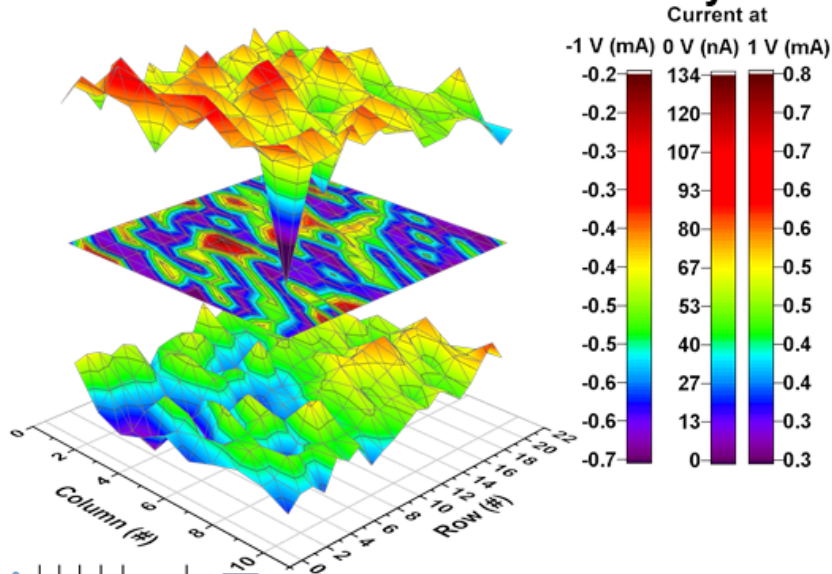


Indicator	Property	Ideal value
Uniformity	Each ratio of 0 and 1 in a dichotomously divided state	50 %
Inter-Hamming distance (HD)	Evaluation of unequal outputs for equal inputs of each device	50 %

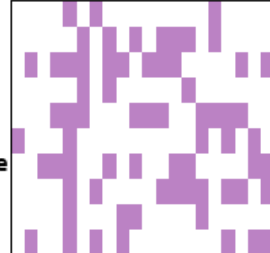
Physically Unclonable Functions

Generate security keys

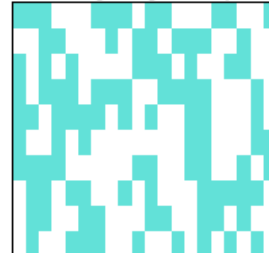
Current distribution at 20 X 10 arrays



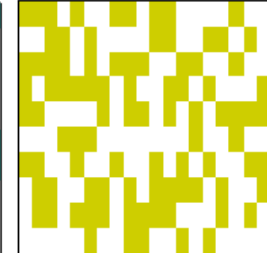
Security key at -1, 1 V



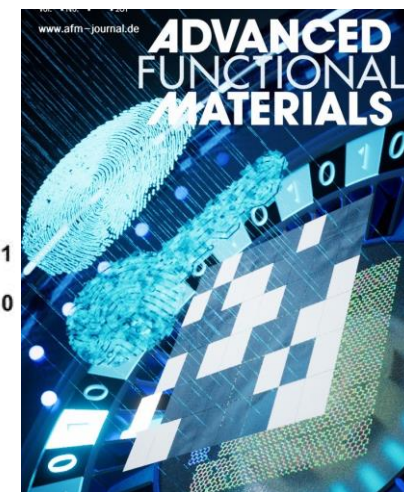
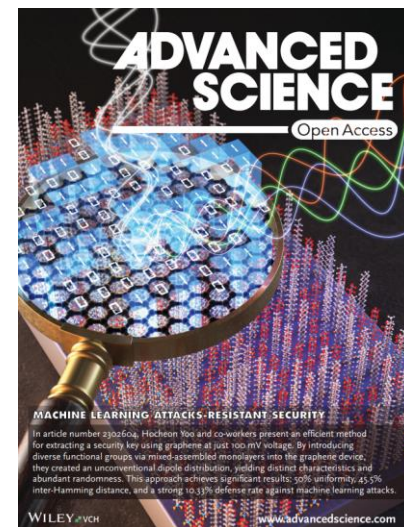
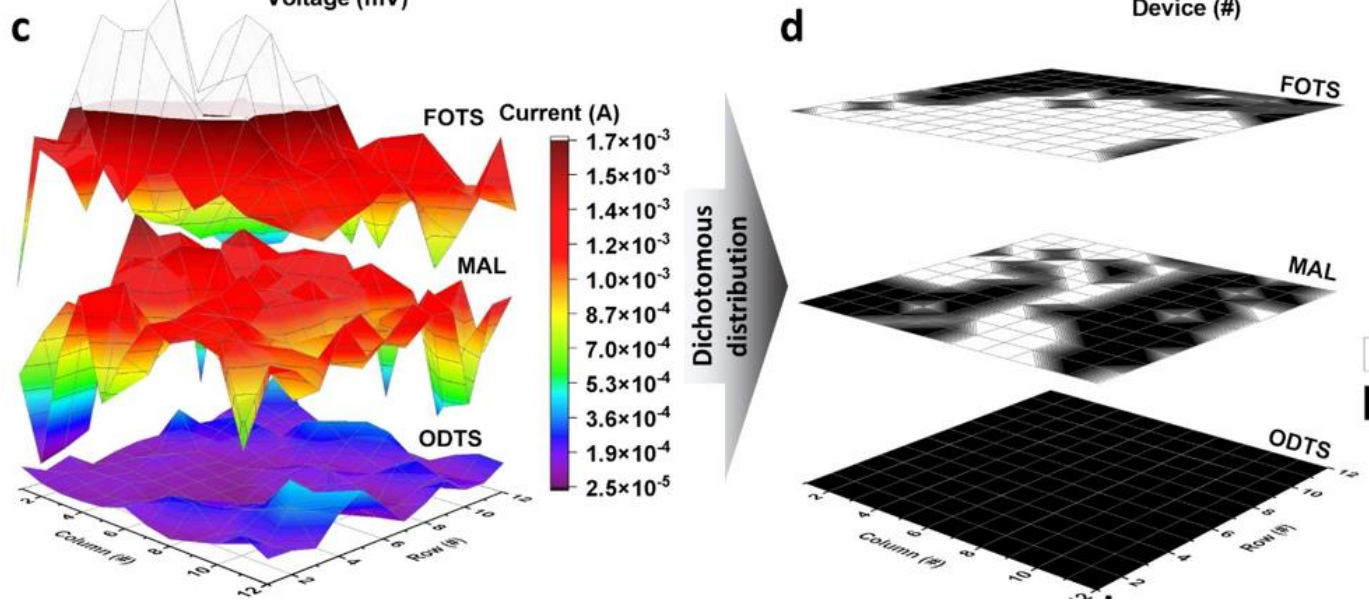
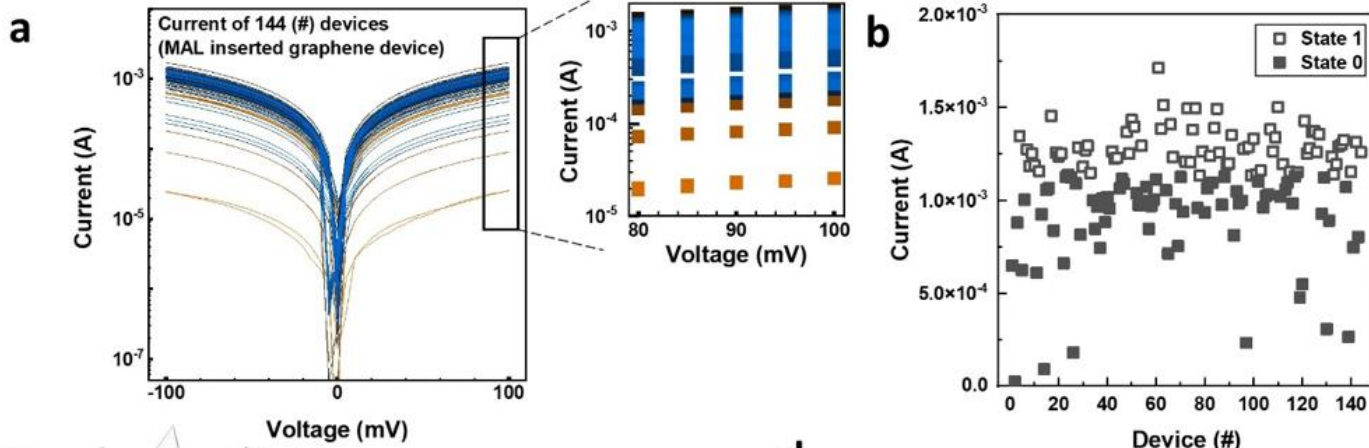
Security key at -1, 0 V

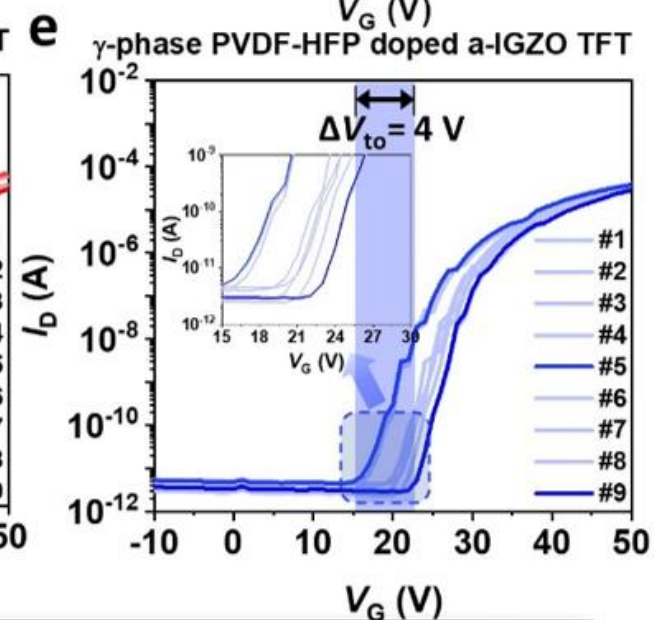
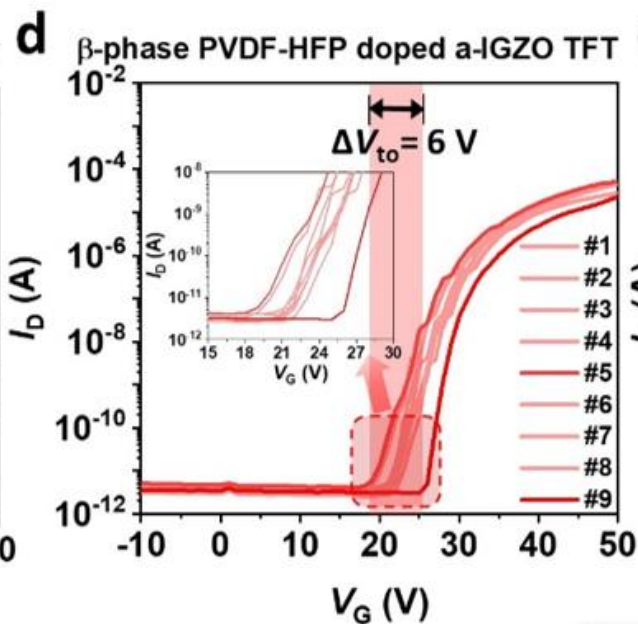
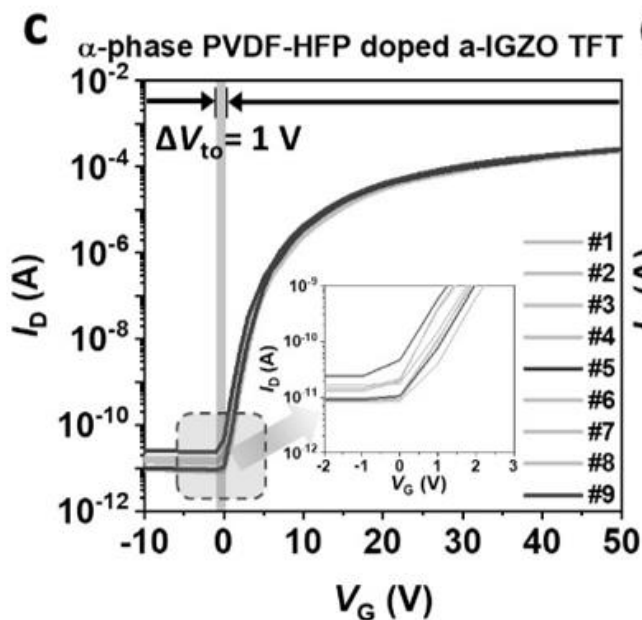
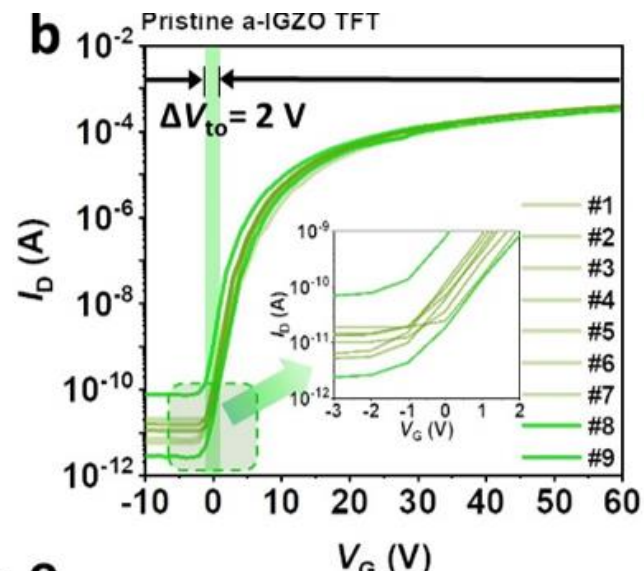
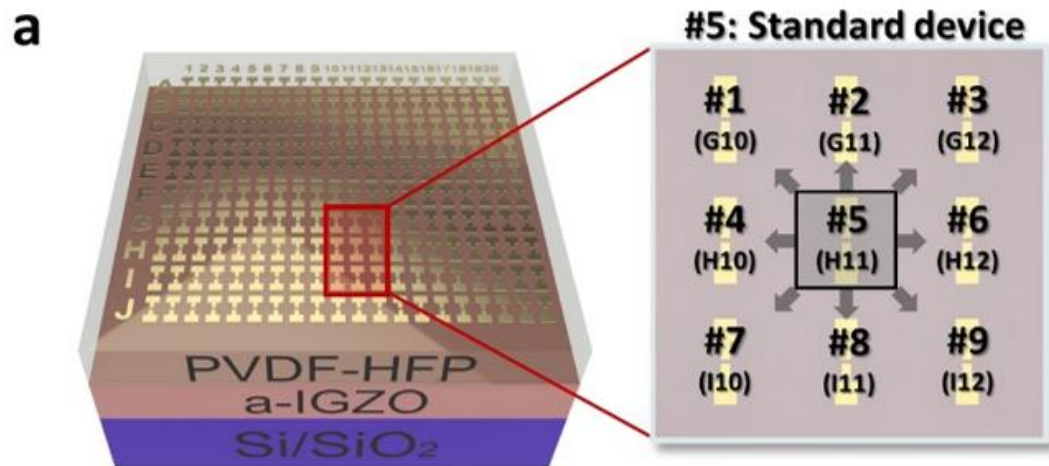


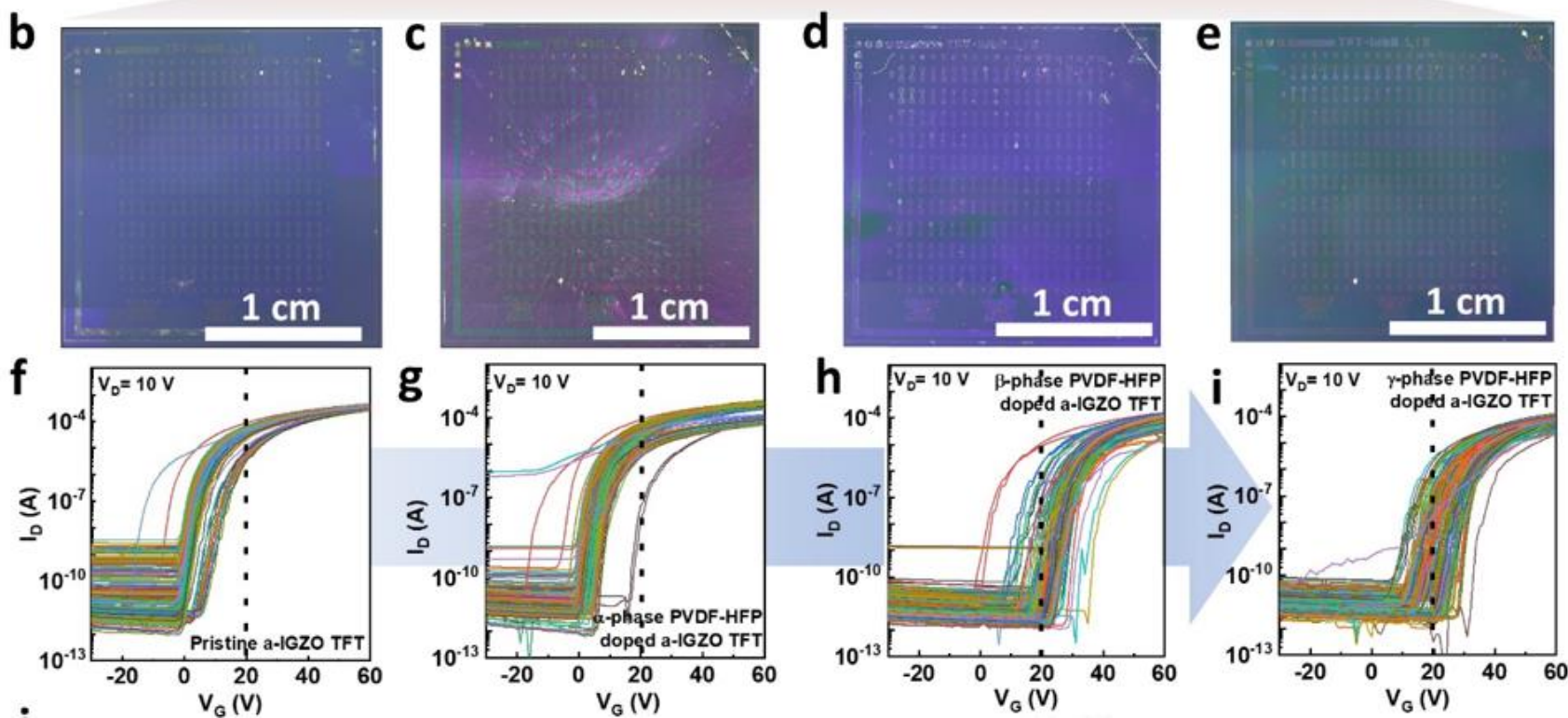
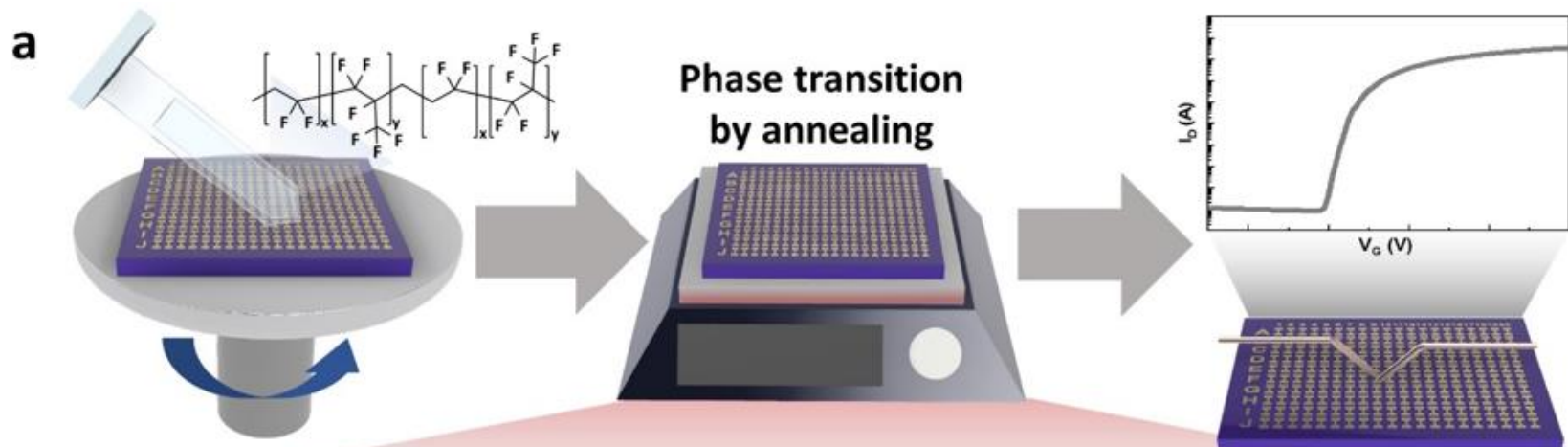
Security key at 0, 1 V

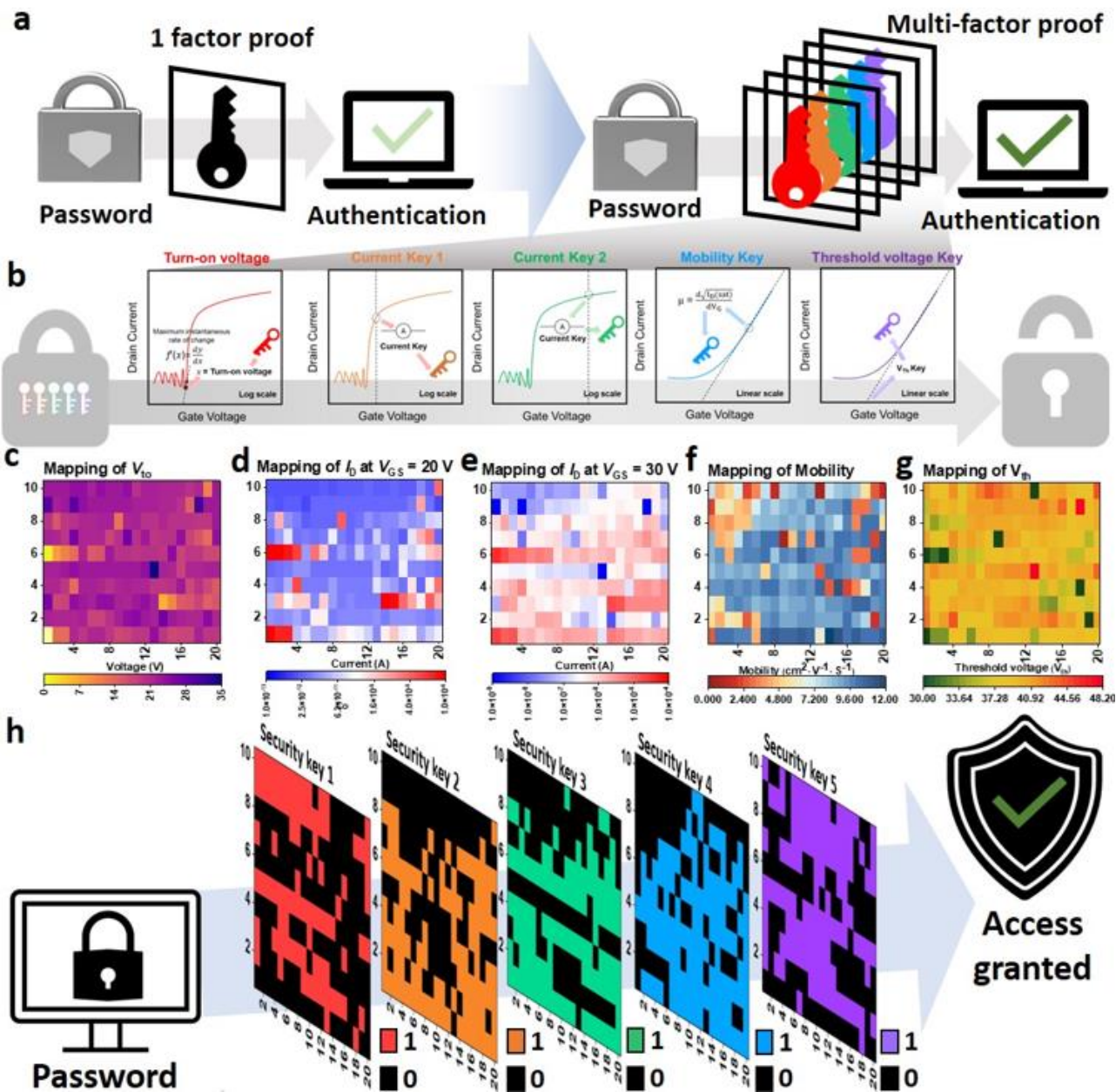


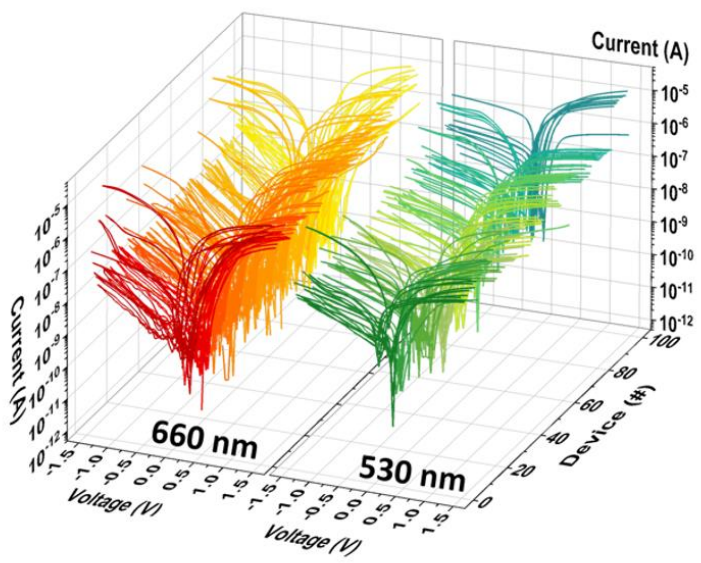
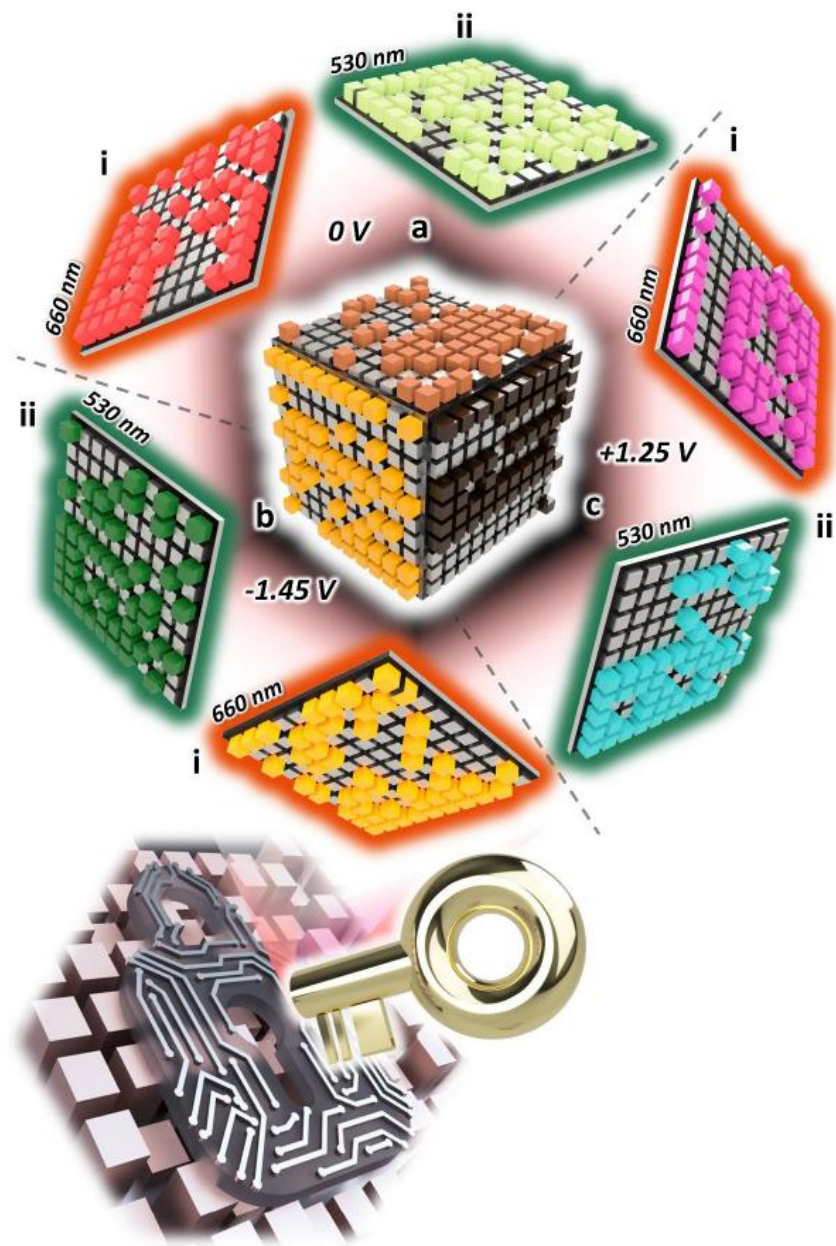
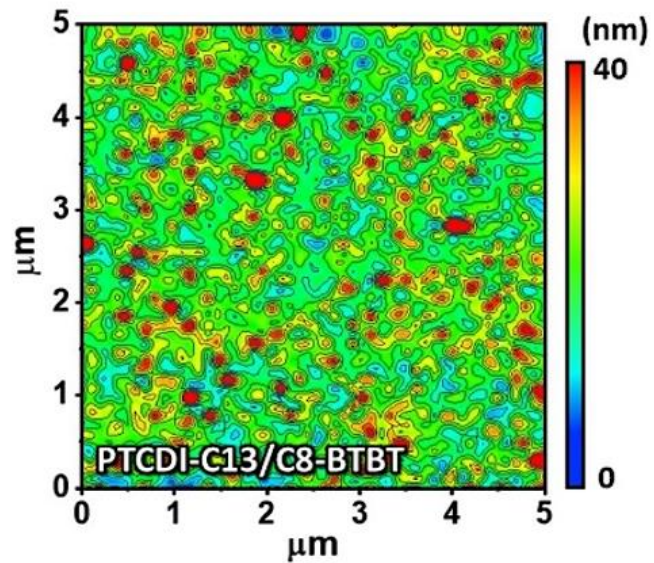
Physically Unclonable Functions

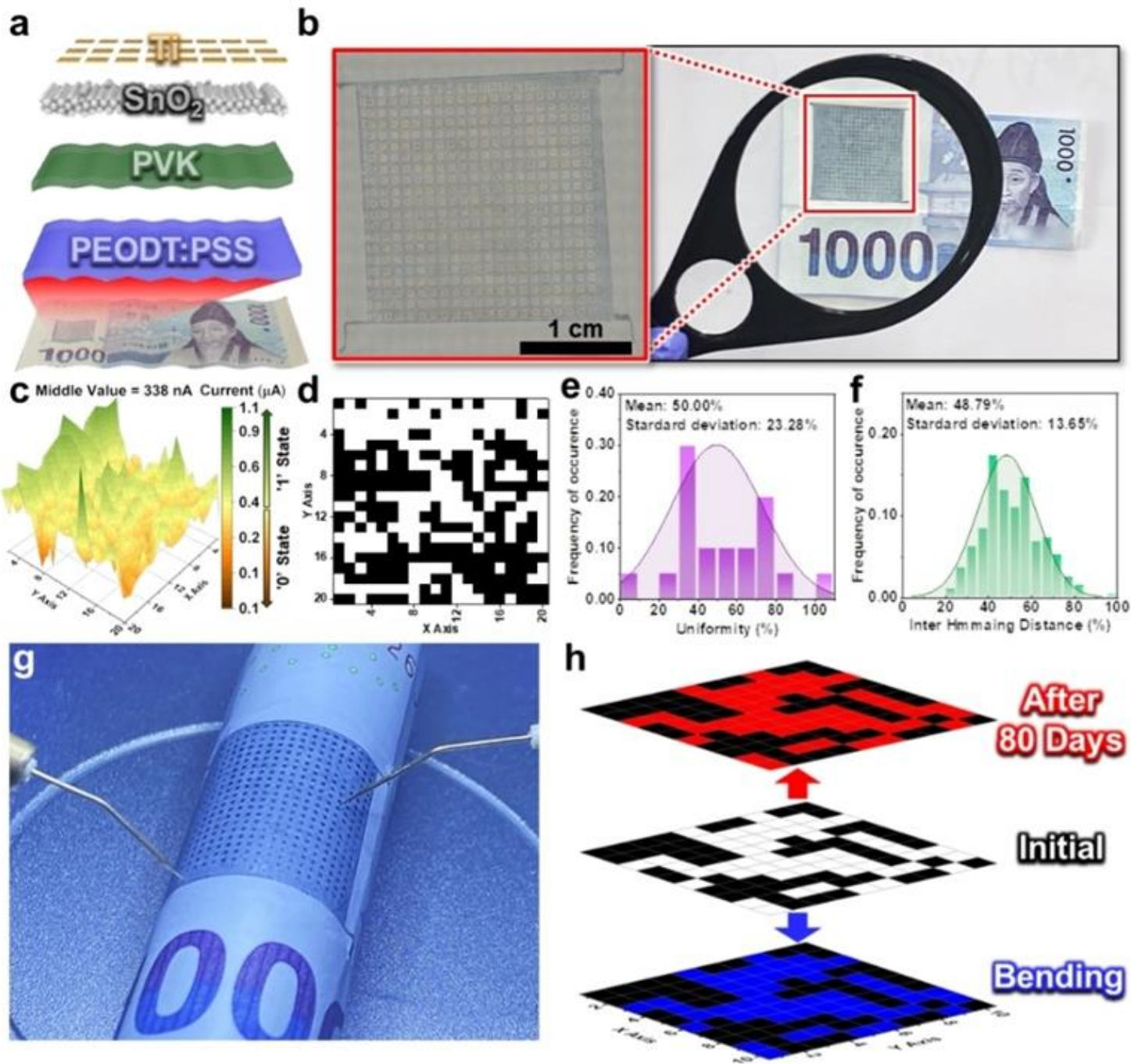








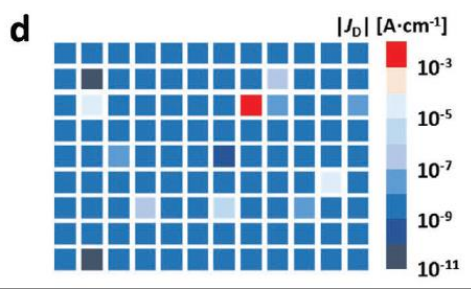
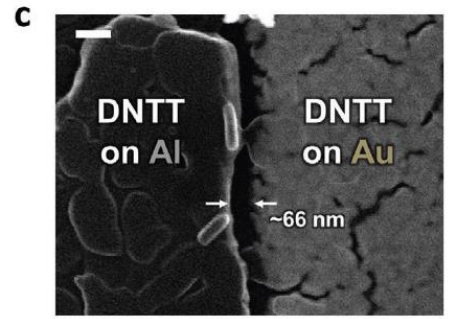
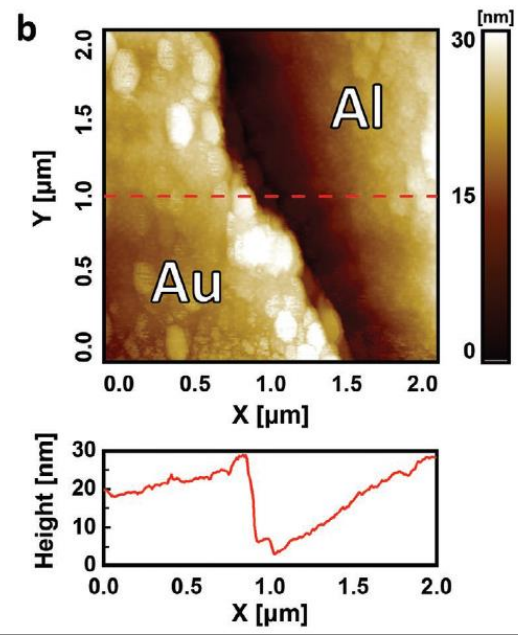
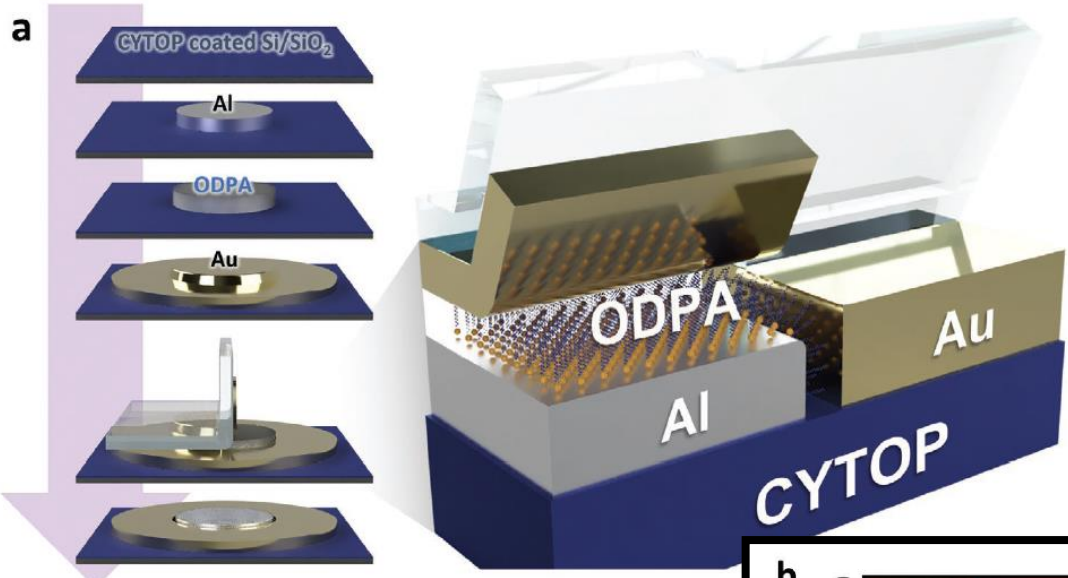




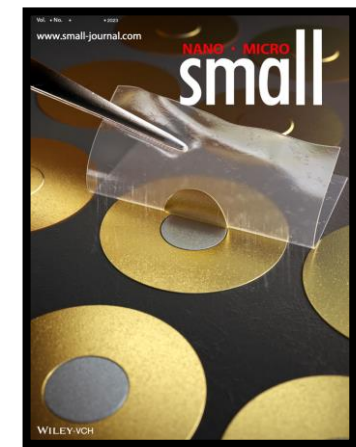
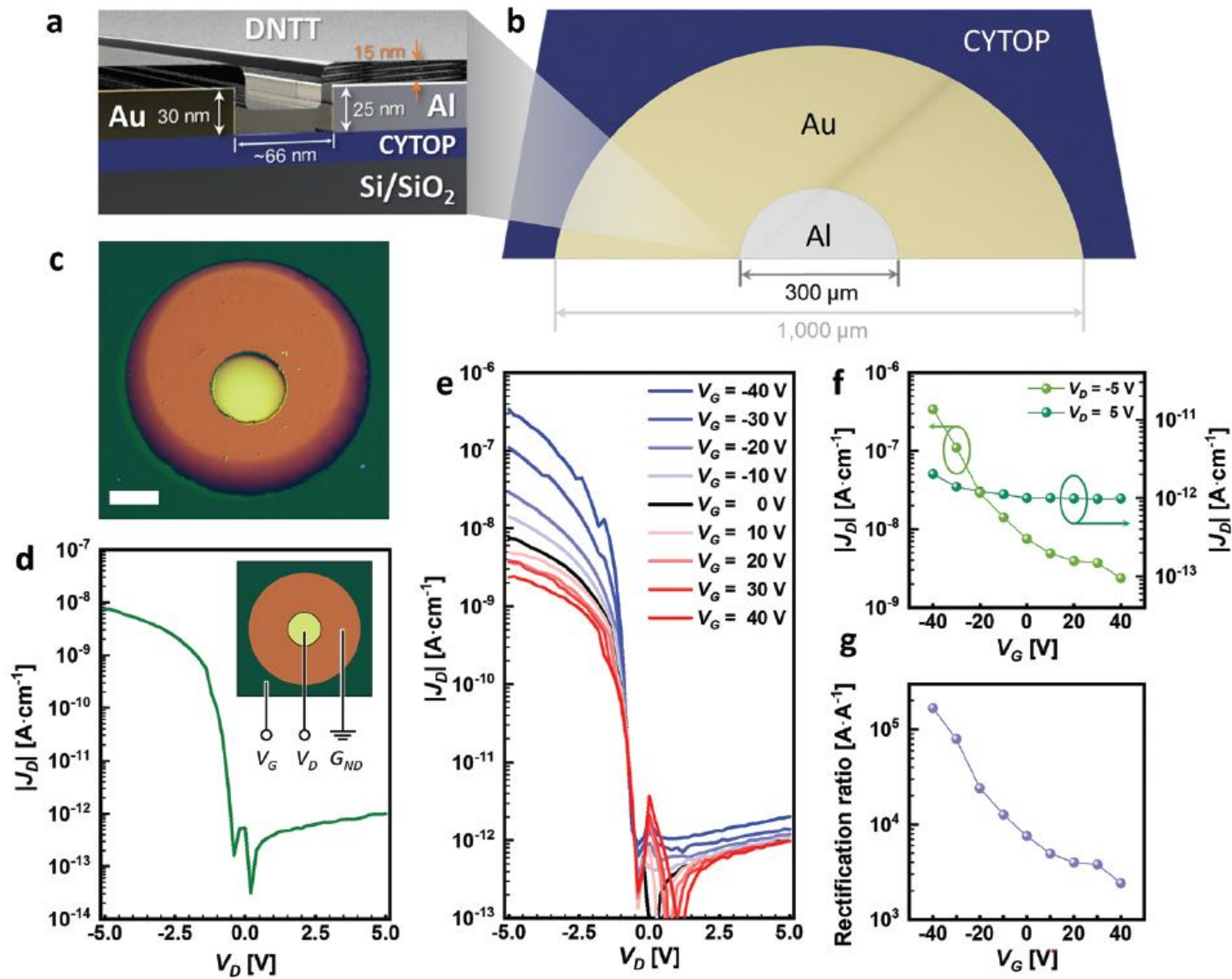
Unpublished results

Nanopattern by adhesion litho (tape)

a



Nanopattern by adhesion litho (tape)



Thank you very much for your attention!



Please contact me by following email:
hyoo@gachon.ac.kr

Homepage: <https://sites.google.com/view/sdclab/>